



Flexible Large Area Electronics and Photonics

From Electronics Only There to Electronics Everywhere

T. N. Jackson

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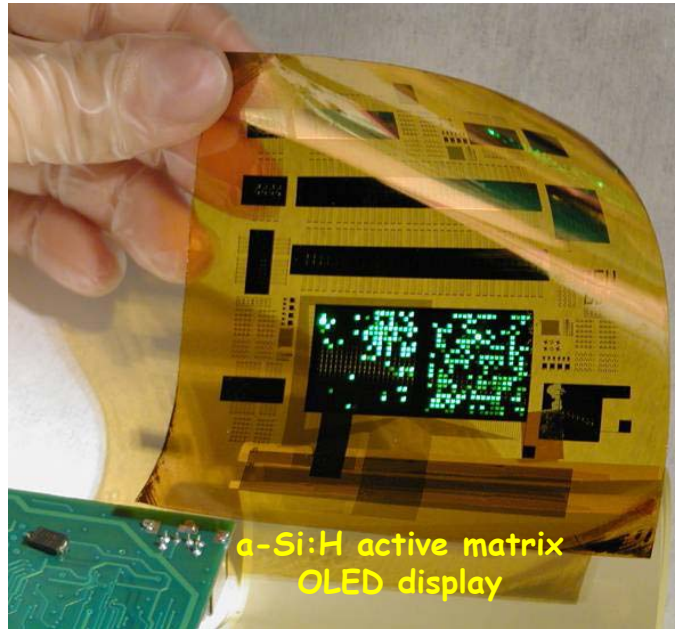


Current Jackson Group members:

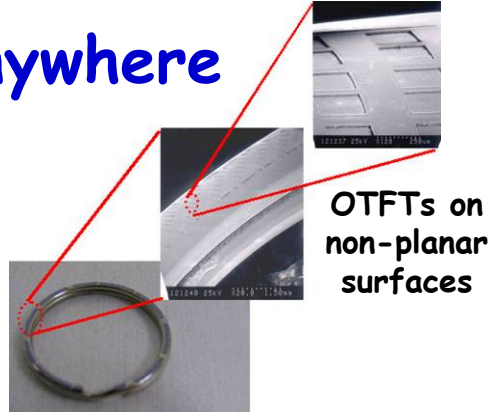
- **Professor:** Thomas N. Jackson
- **Ph.D. students:** Bo Bai, Ying-Ming Huang, Hyunsoo Kim, Sung Kyu Park, Matt Smith, Jie Sun, Yi Zhang, Dalong Zhao, Lisong Zhou
- **M.S. students:** Ho Him Raymond Fok, Arhan Gunel
- **Undergraduates:** Sudhanshu Gakhar



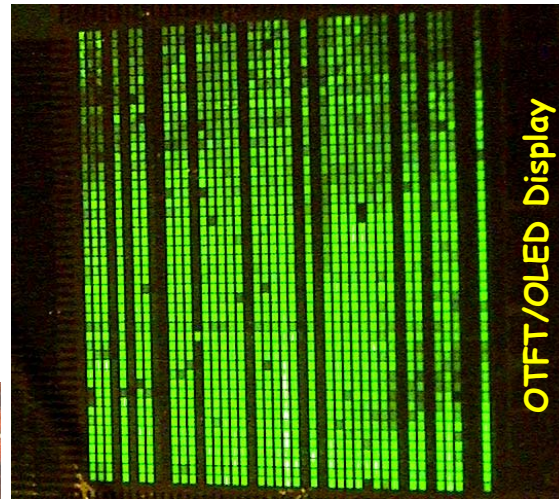
Electronics anywhere



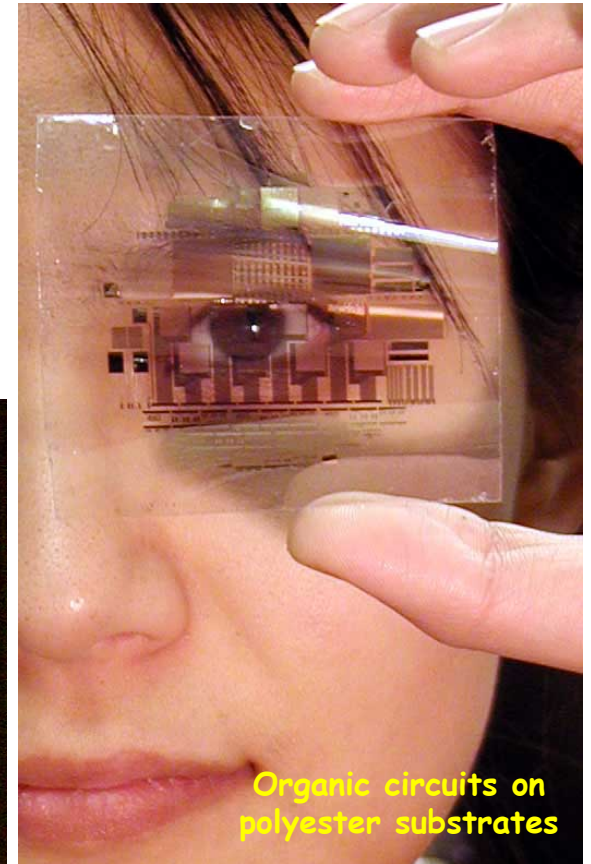
α -Si:H active matrix OLED display



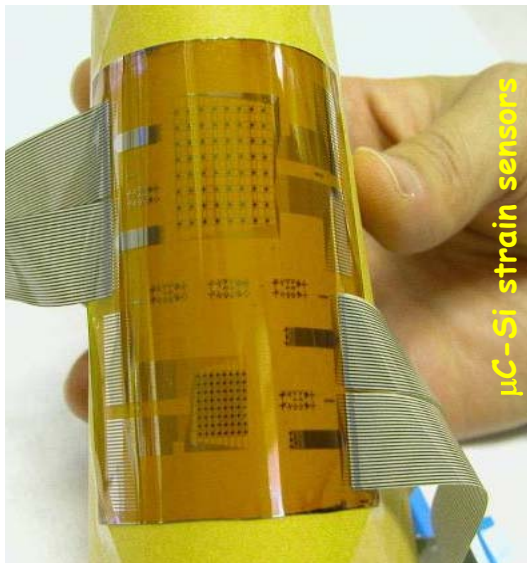
OTFTs on non-planar surfaces



OTFT/OLED Display



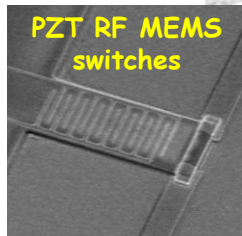
Organic circuits on polyester substrates



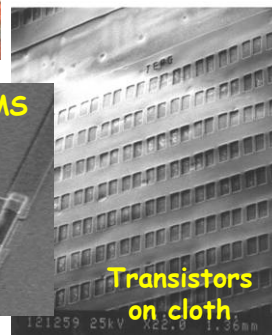
μ C-Si strain sensors



Transistors on cloth



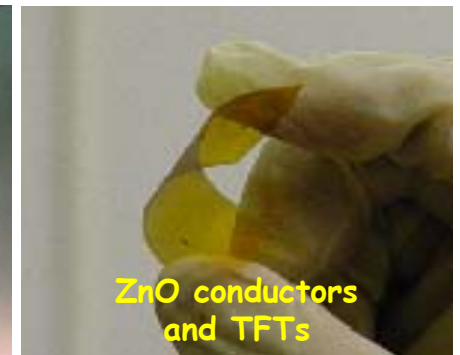
PZT RF MEMS switches



Transistors on cloth



Organic PDLC display



ZnO conductors and TFTs



Moore's Law – The End

Moore's law is now largely irrelevant

Increasingly, computation, control, communication, et cetera are "free" on the scale of the problem being solved

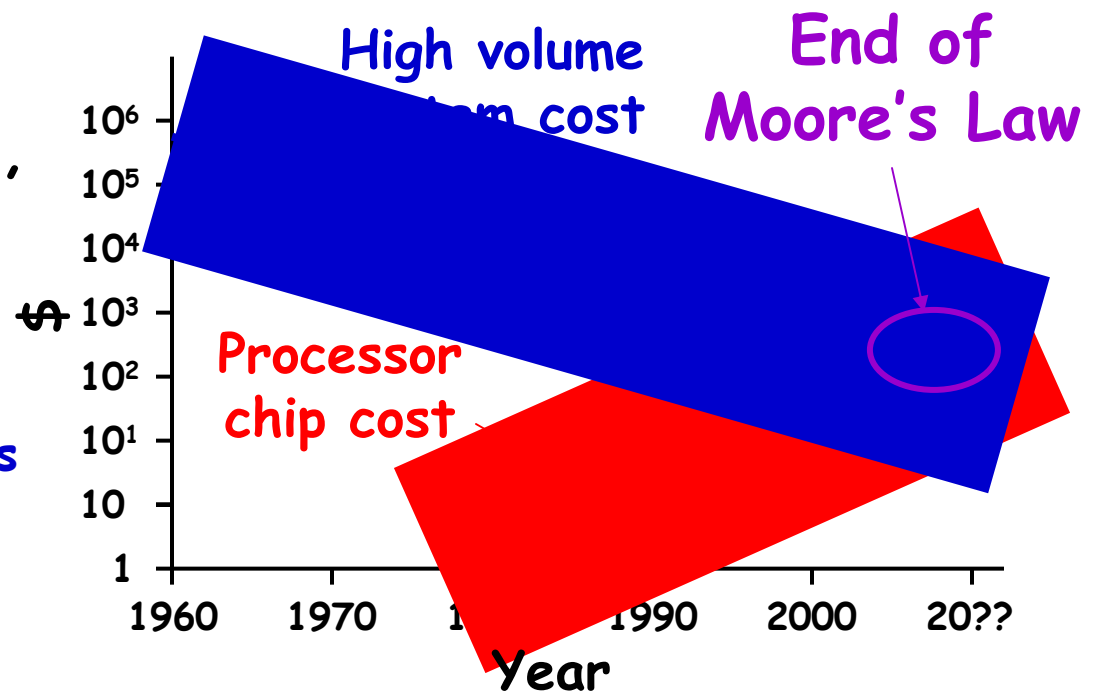
Furthermore, it's ending

Forget the red brick wall, worry about Maly's law

Clarke's first law:

When a distinguished but elderly scientist states that something is possible he is almost certainly right. When he states that something is impossible, he is very probably wrong.

Arthur C. Clarke in *Profiles of the Future*

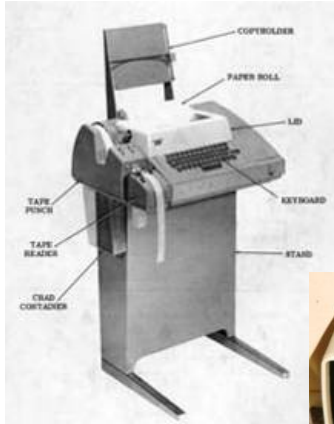


Elderly: In physics, mathematics and astronautics it means over thirty; in other disciplines, senile decay is sometimes postponed to the forties. There are of course, glorious exceptions; but as every researcher just out of college knows, scientists of over fifty are good for nothing but board meetings, and should at all costs be kept out of the laboratory.

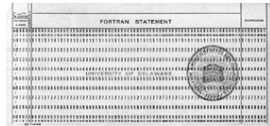
Arthur C. Clarke in *Profiles of the Future*



Example: displays



Primordial ooze



EGA
640x350
16 colors

CGA
320x200
4 colors



VGA
640x480
16 colors

XGA
1024x768
16b color

SXGA
1280x1024
32b color



UXGA
1600x1200
32b color



WUXGA
1920x1200
32b color

QWUXGA
3840x2400
32b color



Samsung 82", HDTV, $\sim 12.5 \times 10^6$ TFTs



For thin film electronics the future is here

**Yearly area of semiconductor electronics in
active matrix displays exceeds IC area**

**Amorphous silicon is now second only to single crystal silicon in
economic importance (far beyond III-Vs, SiGe, et cetera)**



**New Samsung Gen VII display
line (one factory) will produce
an area of active electronics
equal to ~10% of the worldwide
total IC area**

**60,000 1870 mm x 2200 mm
panels/month**

$\sim 3 \times 10^6 \text{ m}^2/\text{year}$ (~ 730 acres)

$\sim 0.1 \text{ m}^2/\text{s}$ of finished work

$\sim 5 \times 10^6 \text{ kg}$ of glass/year



**N.B.: for flexible large area electronics
and photonics this is the competition**



Old paradigm: bring the problem to solution in single crystal semiconductors

New paradigm: take the microelectronic solution to the problem

To take the solution to the problem:

- size matters
- form factor matters
- material matters
- process matters
- function matters
- cost matters matters matters

Performance is determined by application and context



Example: Smart dressing

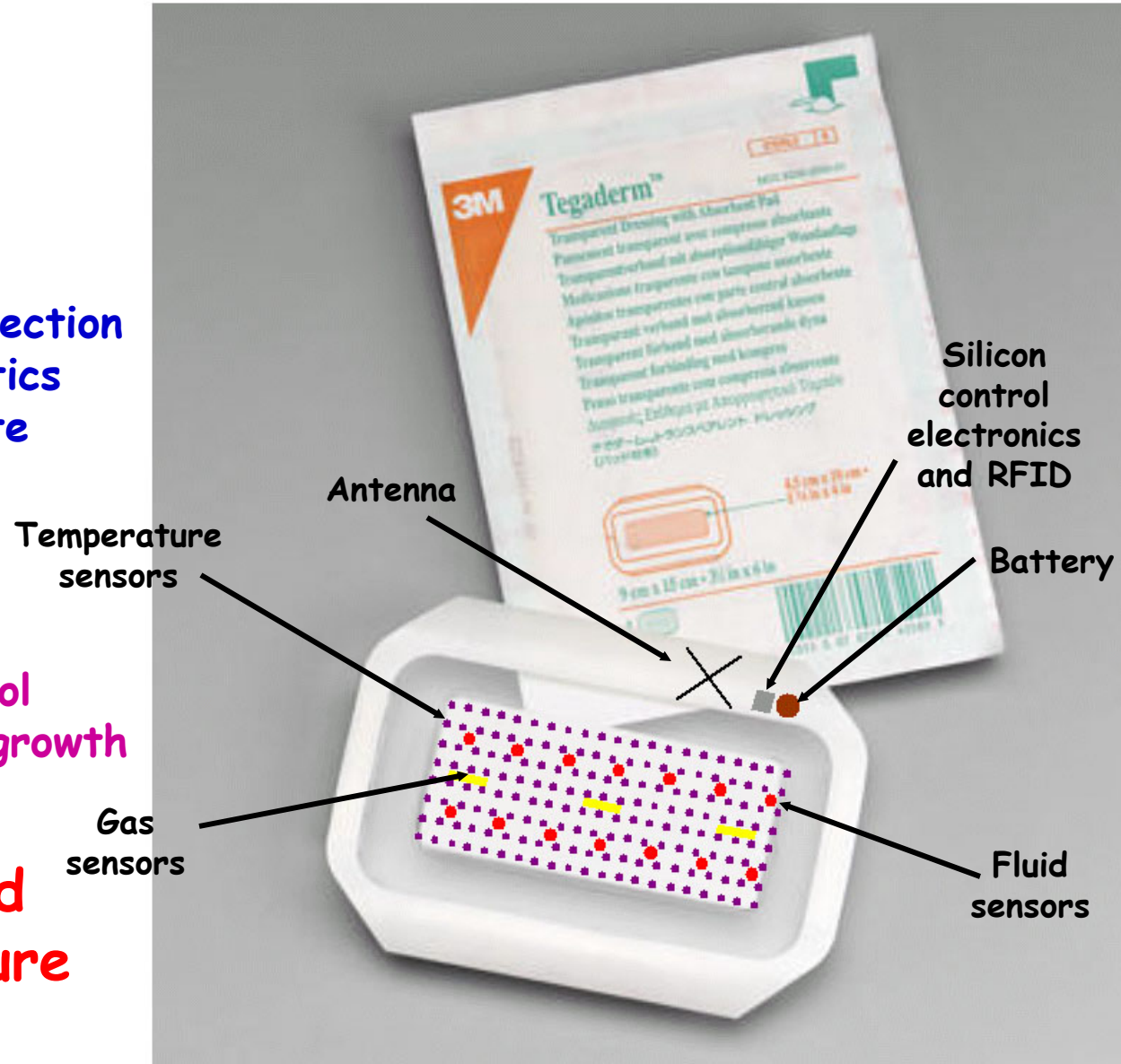
Sense:

- Infection
- Leakage
- Rejection
- Early problem detection
- Improved diagnostics
- Reduced error rate
- Improved system integration

Active therapy:

- Local drug control
- Stimulated cell growth

Low-cost and low-temperature are drivers

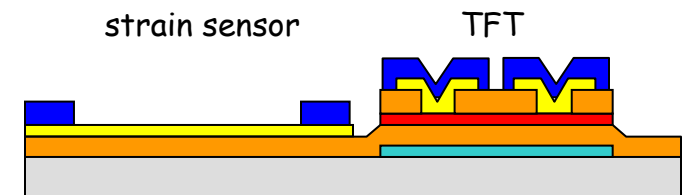
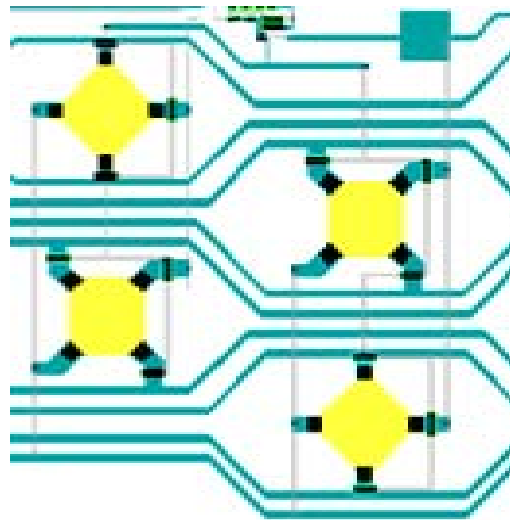




Example: sensor arrays

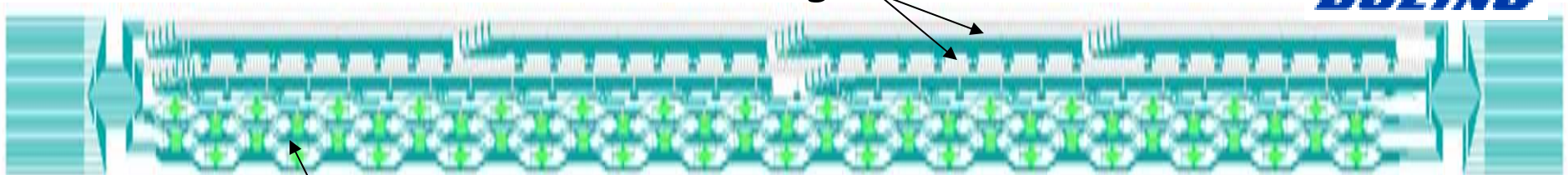


- Flexible semiconductor strain sensor
- TFTs for sensor selection and isolation
- Large area shape and strain sensing
- Structural health monitoring
- Many other sensor types possible



100" demo
100' application

sensor select decode logic

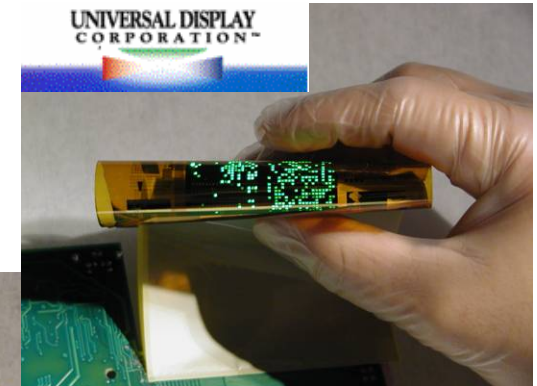
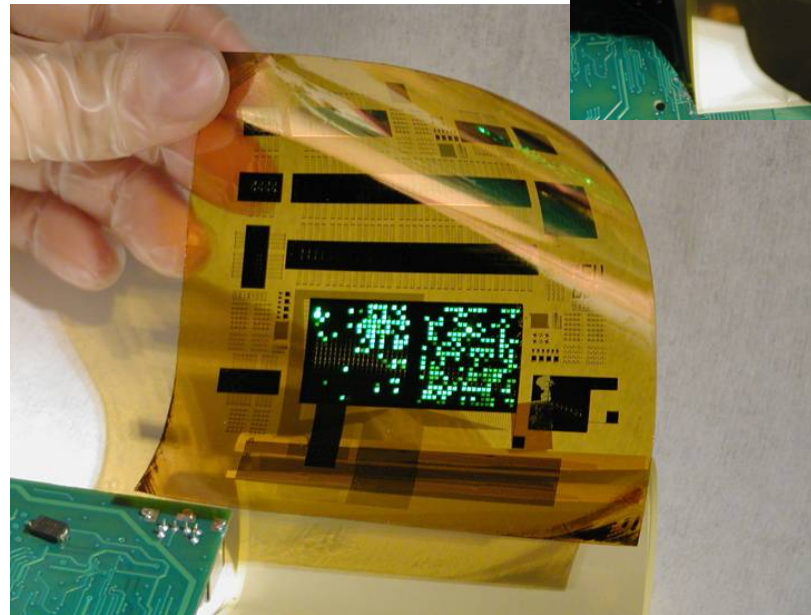


strain sensors (15 columns of 4 sensors)



Form Factor Matters

Example: Displays



Light-weight, rugged, flexible displays

Displays on curved and arbitrary surfaces

Advantages for sensor arrays similar



Example: Soft Materials

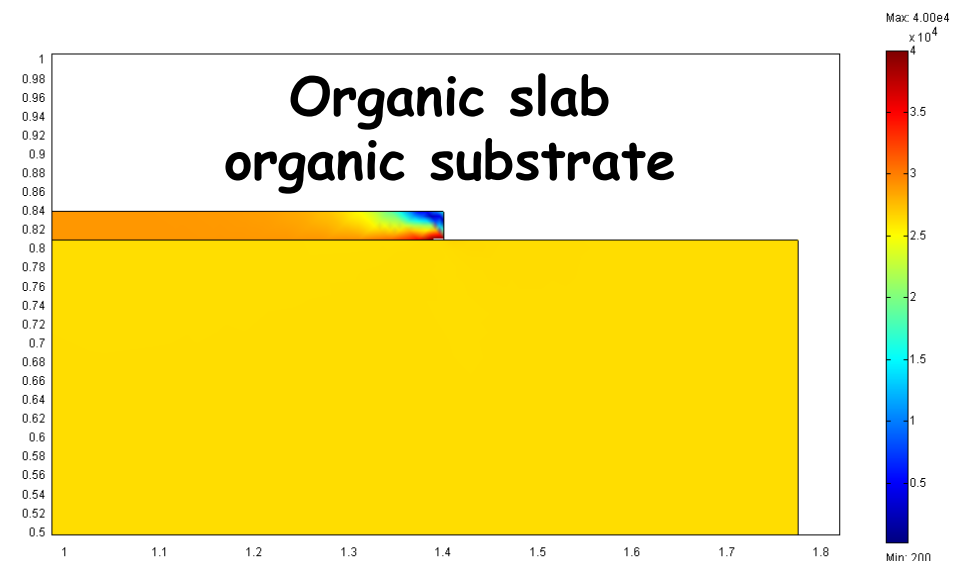
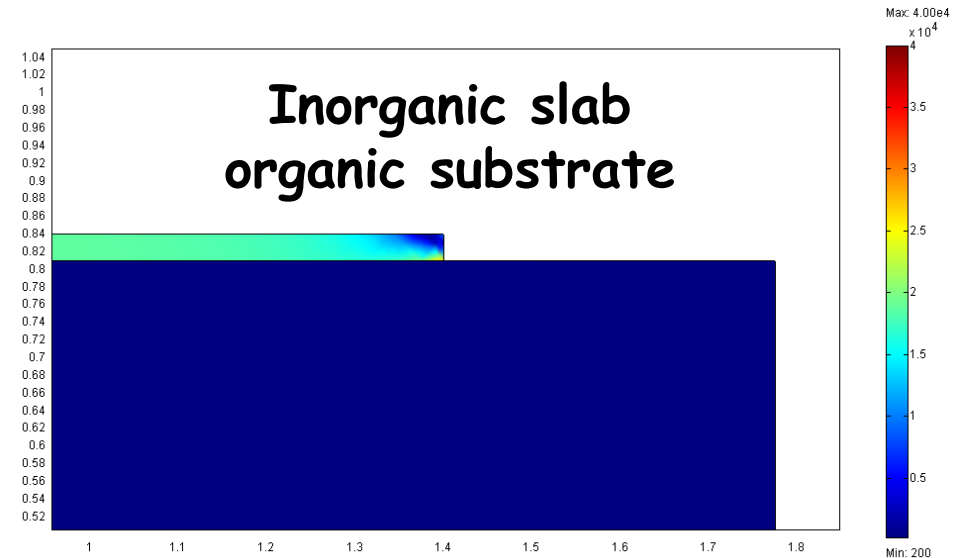


Increasing use and importance of soft materials

Sensors and actuators matched to material can provide performance and reliability advantages

Match Young's modulus, acoustic, thermal characteristics, et cetera

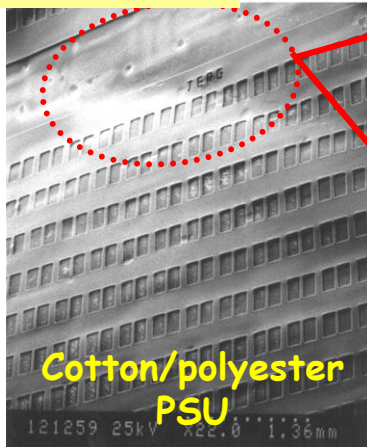
Soft bio-implantable electronics



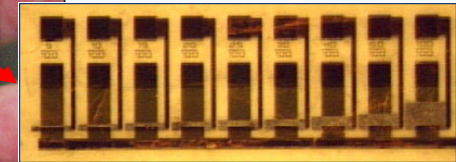
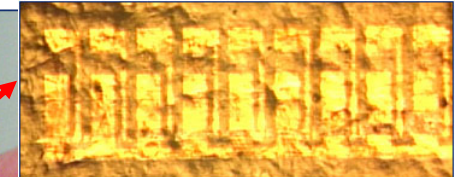


Example: electronics on low temperature materials

cloth



paper



Displays; active camouflage; bio,
chemical, radiation, thermal, and
health sensors on uniforms

Ultra-low-cost electronics

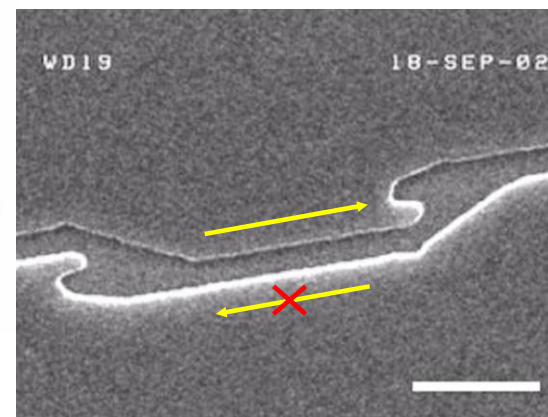
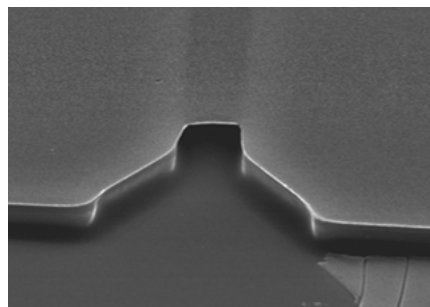
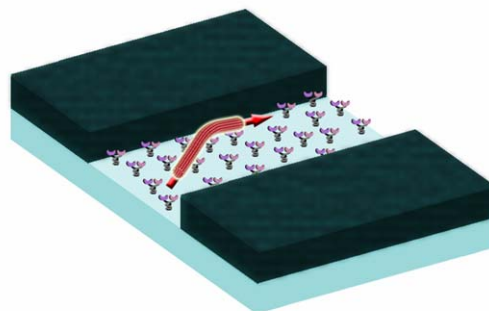
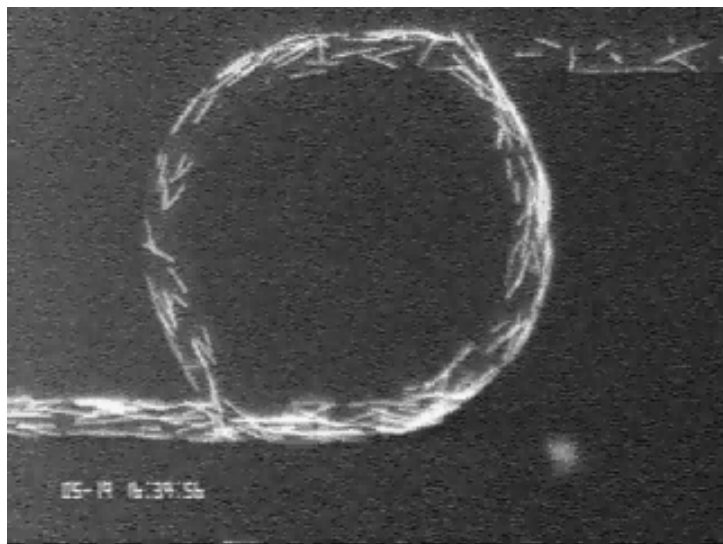




Example: Biophotonics

Collaboration with
Will Hancock
PSU Bioengineering

Microtubules move on surface
functionalized with kinesin motors

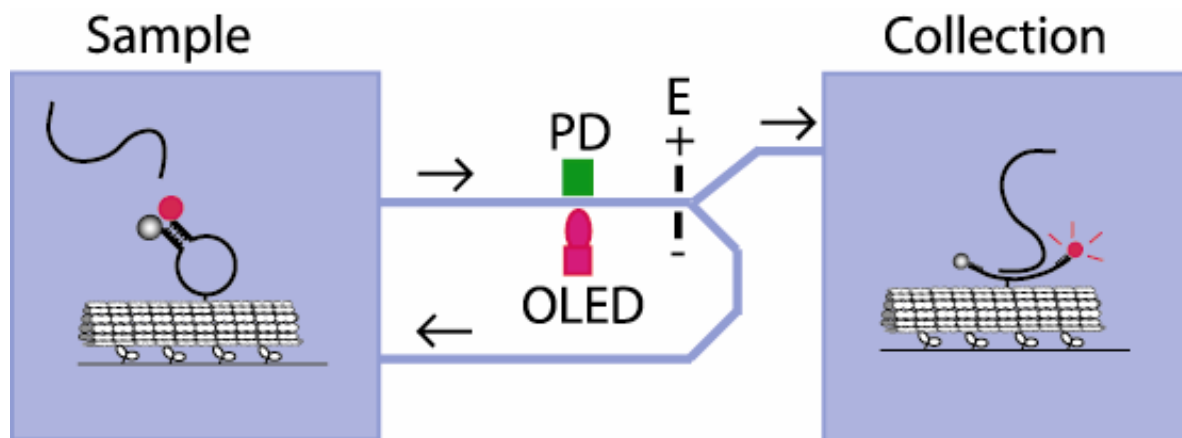


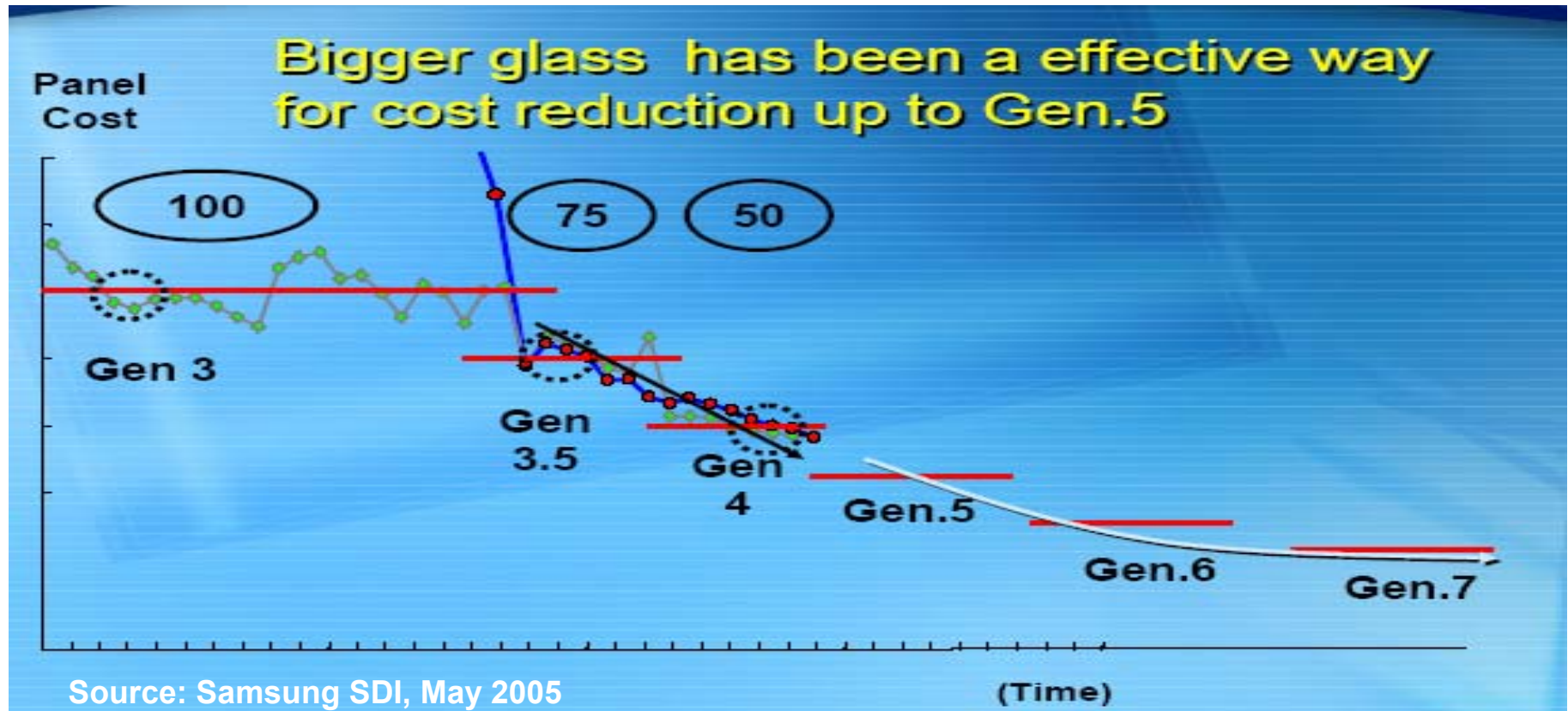
Bio-molecular motors
provide simple
nanoscale motion – avoid
nanofluidic problems

Replace fluorescence
microscope with integrated
sources and detectors

Organic electronics can
provide optical sources,
detectors, and control logic

Chemical and biological
hazard sensing, micro
DNA analysis





Display manufacturing cost follows car pooling rule

New generation effective way to reduce display cost

Ineffective approach for dramatic cost structure change

Note Gen. 7 plant ~ $\$5 \times 10^9$

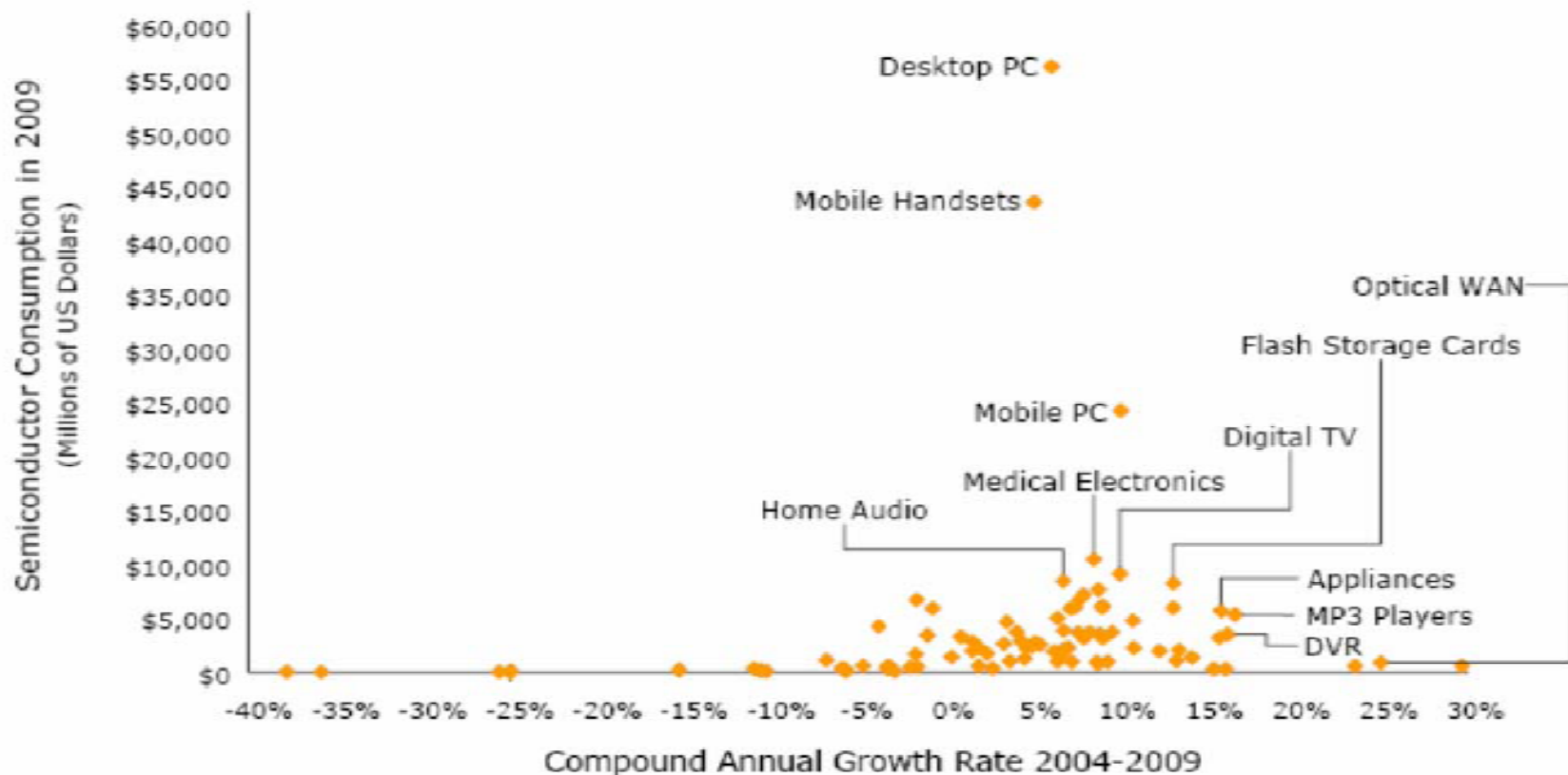


Markets Likely to be Fragmented

More significant problem for large area electronics than for silicon

Semiconductor demand profile

- Other than PCs and handsets, semiconductor demand will be highly fragmented with many markets fading fast...

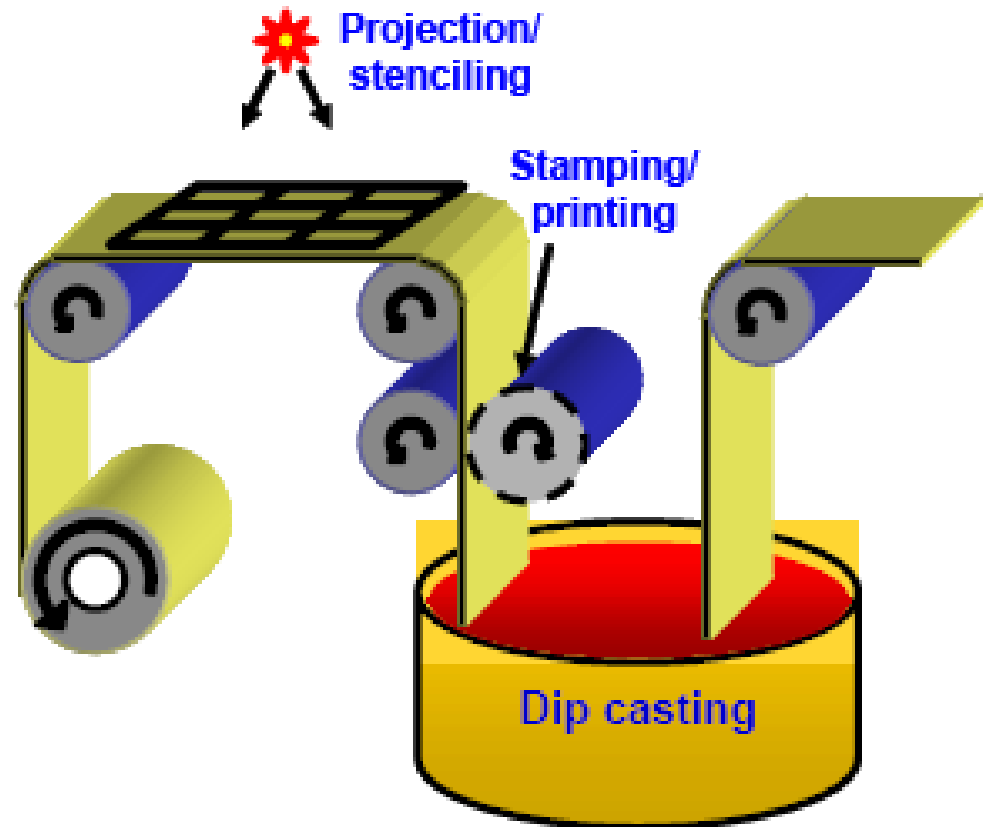


Sources – iSuppli Corporation *Application Market Forecast Tool (AMFT)*™



Opportunity for new processing approaches

- Additive processes
- Low temperature
- Feature size and placement tolerant
- Roll-to-roll process
- High volume production
- Fabrication on arbitrary shape substrates



Cost more important than flexibility

Prediction: Non-Moore's law electronic progress to come
will be as stunning as Moore's law progress has been

Electronics Anywhere -the new frontier-

Baby step:
Flexible Polymeric Substrates

A tale of two substrates

High temperature polyimide - α -Si:H, ZnO

Low temperature polyester - organic TFTs

High temperature polyimide - a-Si:H, ZnO

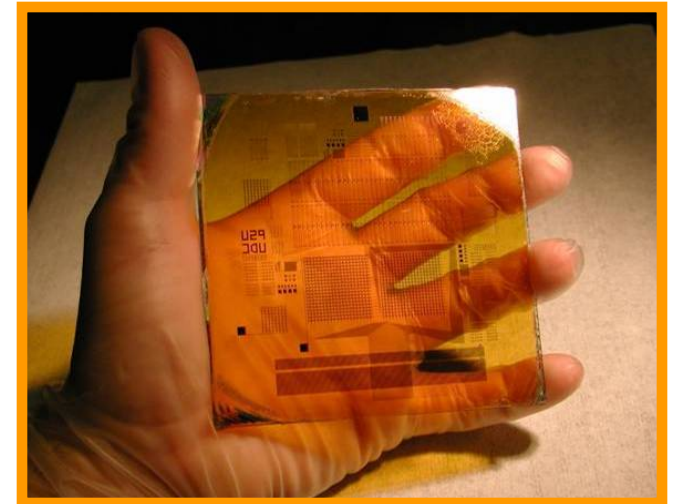
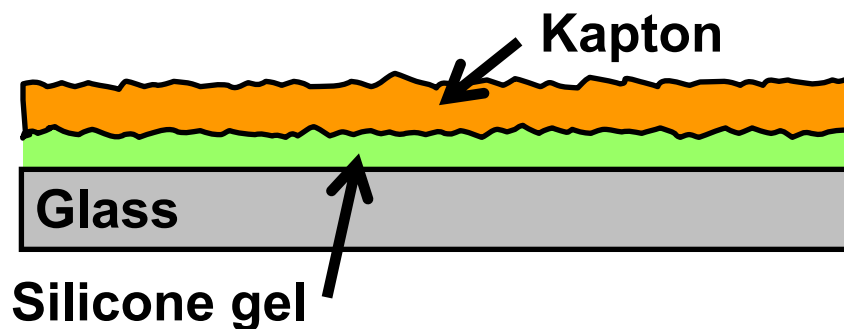
Evolutionary technology

(build on \$100 × 10⁹/year display industry)



Hydrogenated amorphous silicon thin film transistor fabrication

- Polyimide substrates
 - Good thermal and chemical stability
 - ⇒ treat just like glass
- Substrate laminated to glass carrier with pressure-sensitive silicone gel
- Maximum process temperature = 250 °C



Differential-pressure vacuum laminator

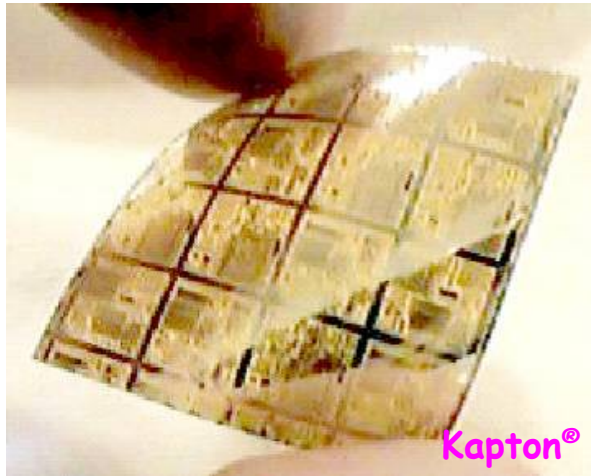


a-Si:H TFT-based Sensors and Circuits

Large area sensors, actuators, displays, et cetera, on arbitrary substrates

Bring microelectronics to the function

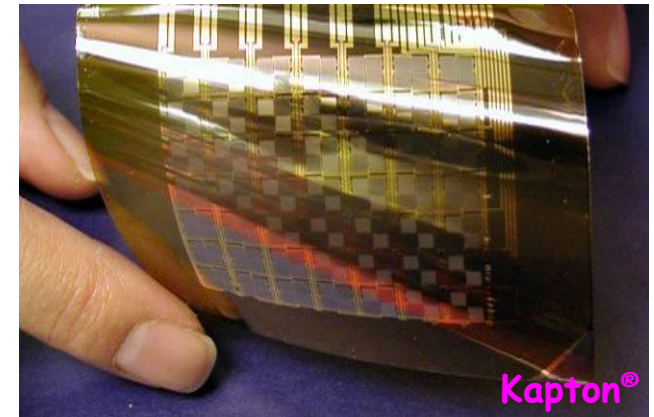
a-Si:H ICs



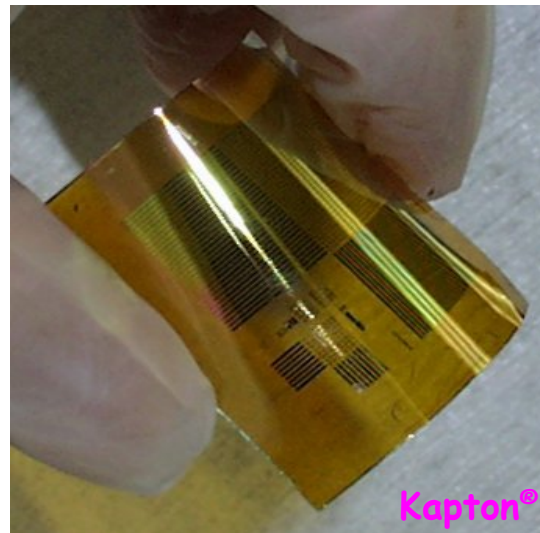
a-Si:H photovoltaics



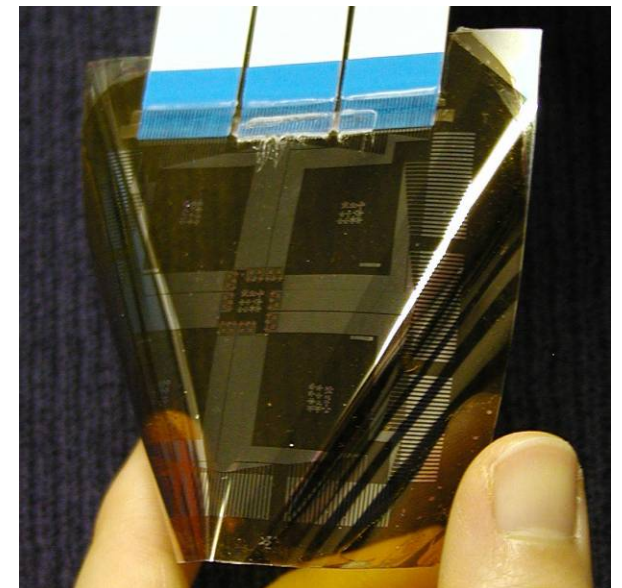
a-Si:H strain bridge array



Transparent polyimide



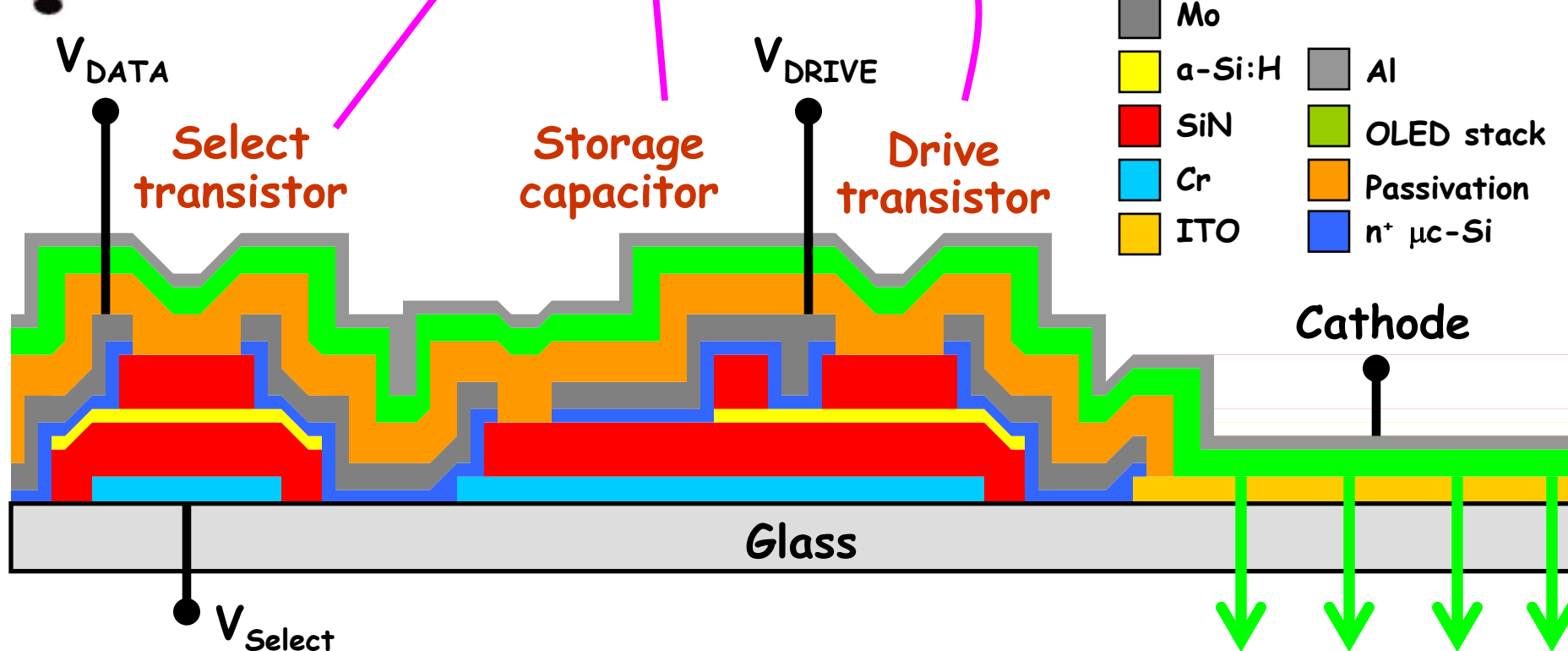
a-Si:H gamma ray detector



μC-Si strain sensors

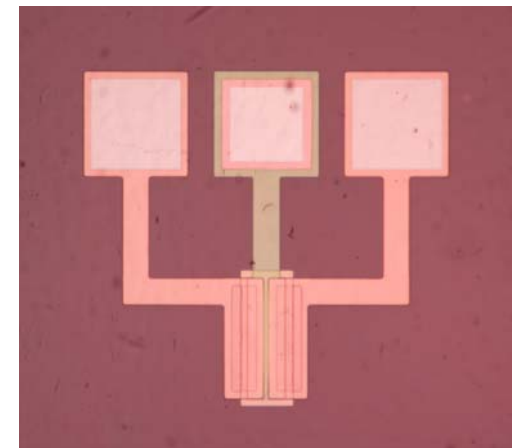
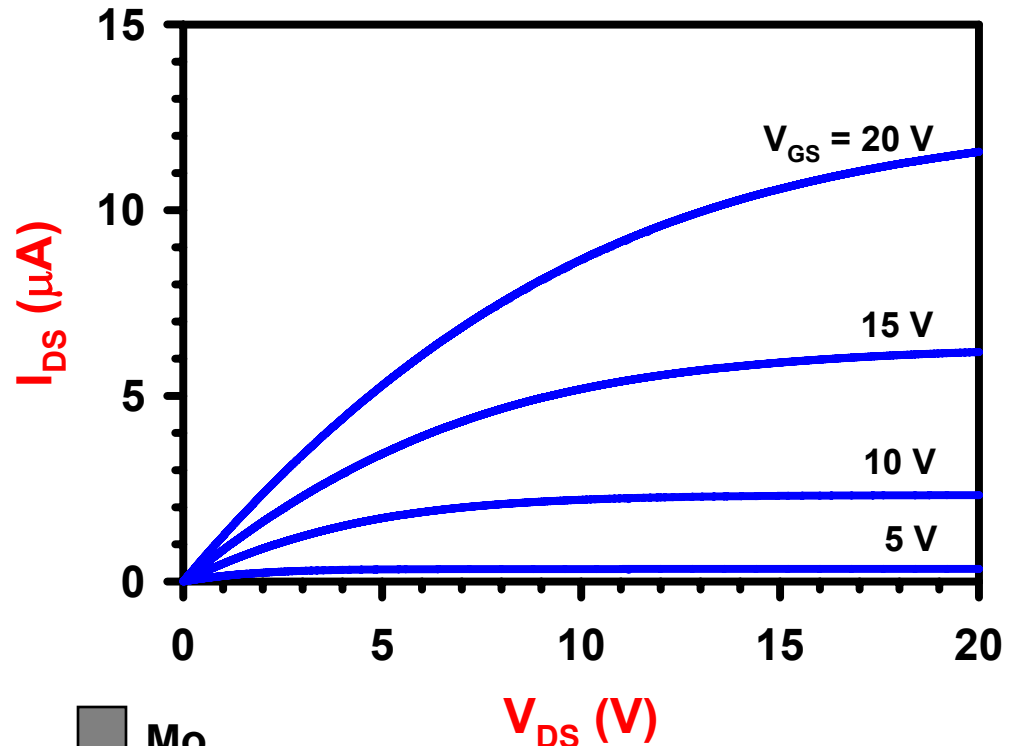
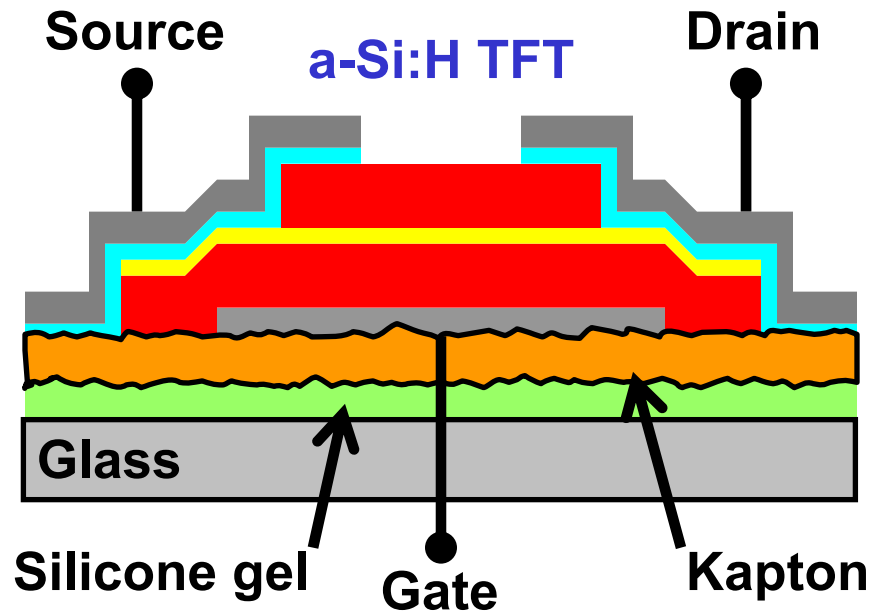


- Inverted staggered tri-layer a-Si:H TFT process
- Silicon nitride layer isolates TFTs and OLEDs
- Green emitting OLEDs



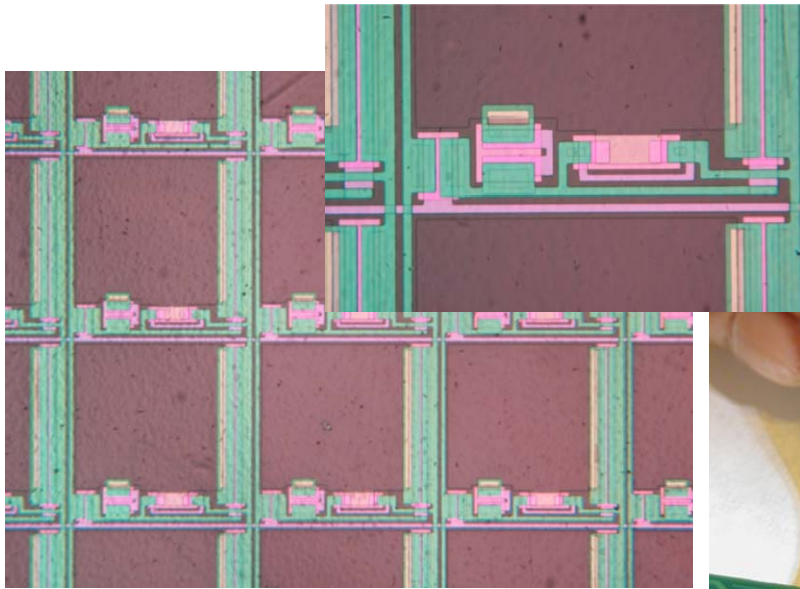


- TFT Performance similar to TFTs fabricated on glass
 - Mobility = $0.8 \text{ cm}^2/\text{V-s}$
 - Threshold voltage = 1.6 V
 - Sub-threshold slope = 0.5 V/decade

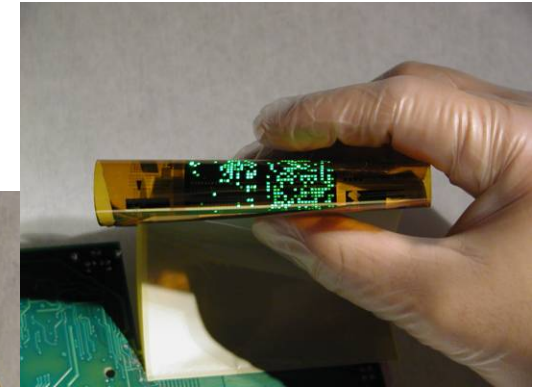
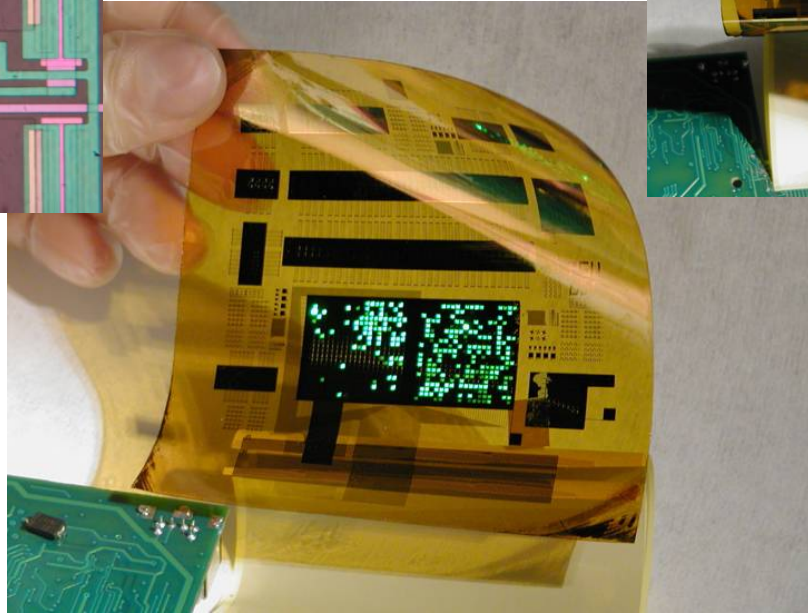




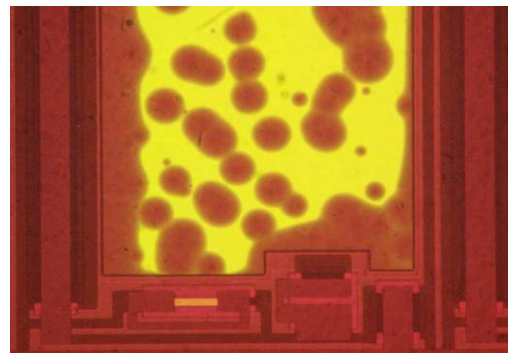
OLED pixels on plastic degraded



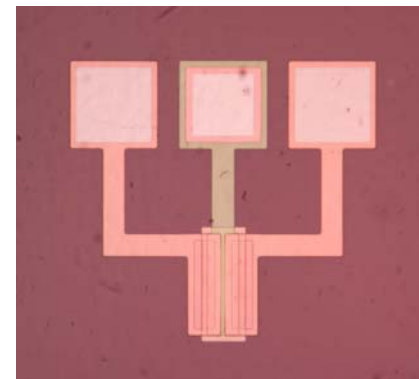
Pixel Array



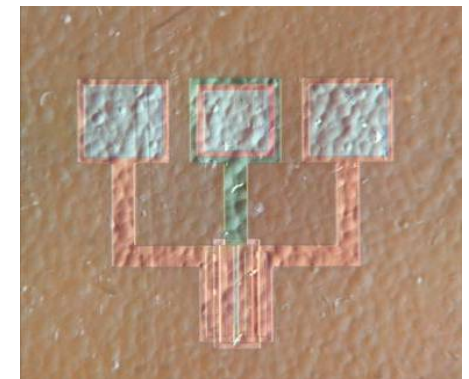
Pixel on Glass



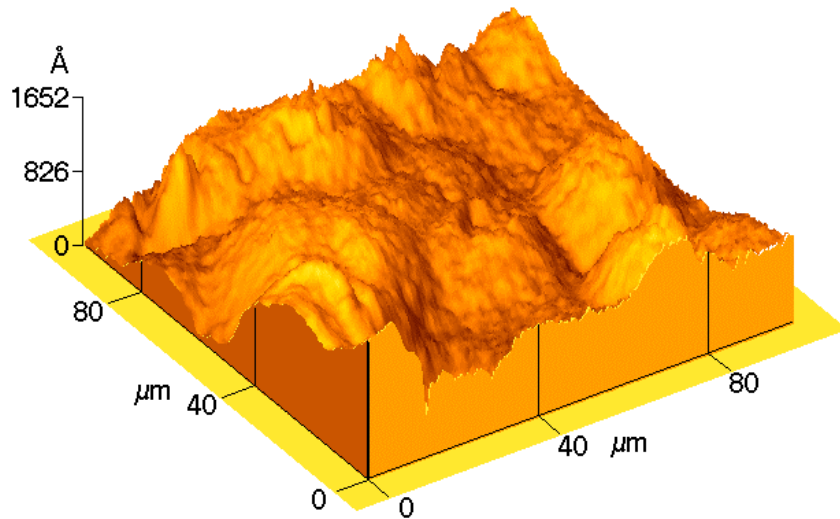
Pixel on Polyimide



Bright field



DIC



~ 30 nm RMS roughness over small areas

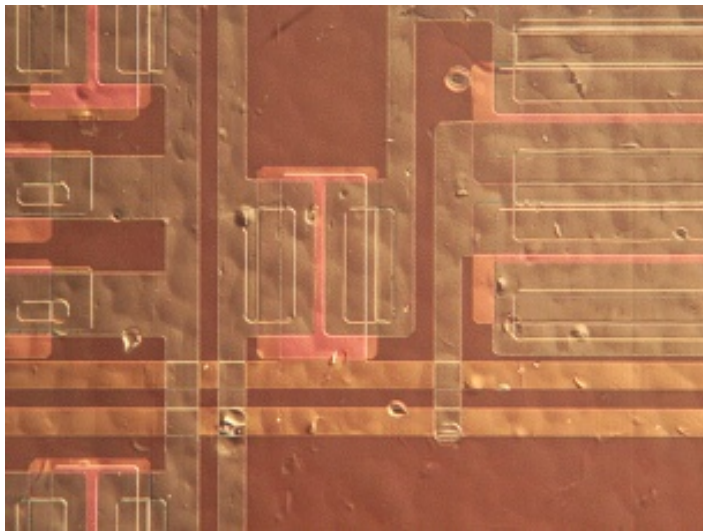
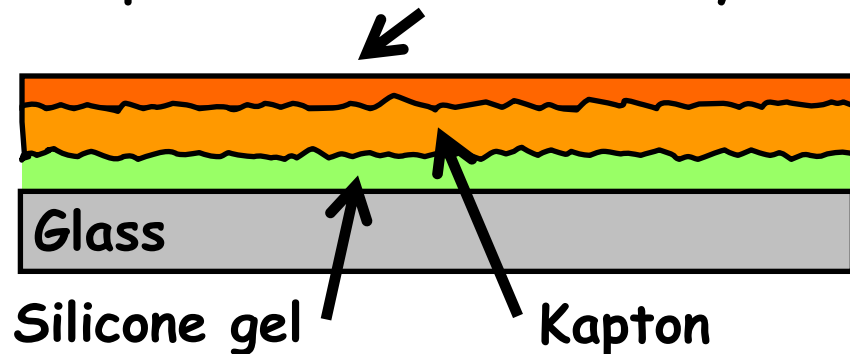
“Rolling hills” topography

Can make heat transfer problematic;
solved by silicone gel mountant

But surface also has sparse,
sharp, high relief features
(also easy to add features)

- Planarization?

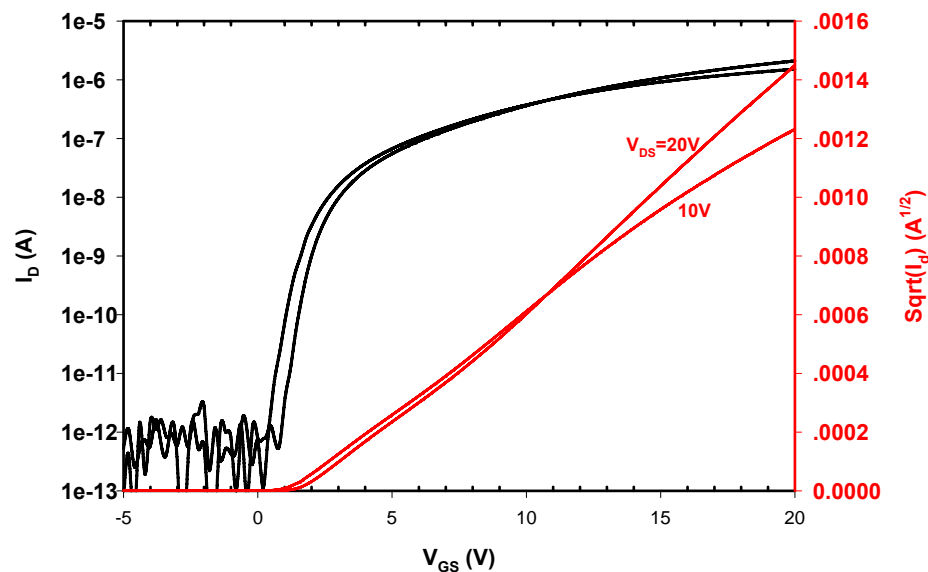
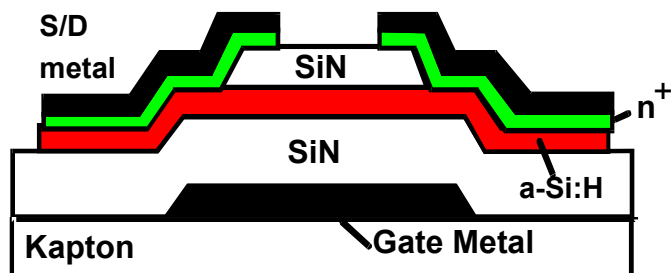
Spin-on Planarization Layer



- Chemical-mechanical polishing?



α -Si:H TFTs fabricated with H_2 dilution at 150 °C



Saturation mobility

1.0 cm²/Vs @ $V_{DS}=20V$

Linear mobility

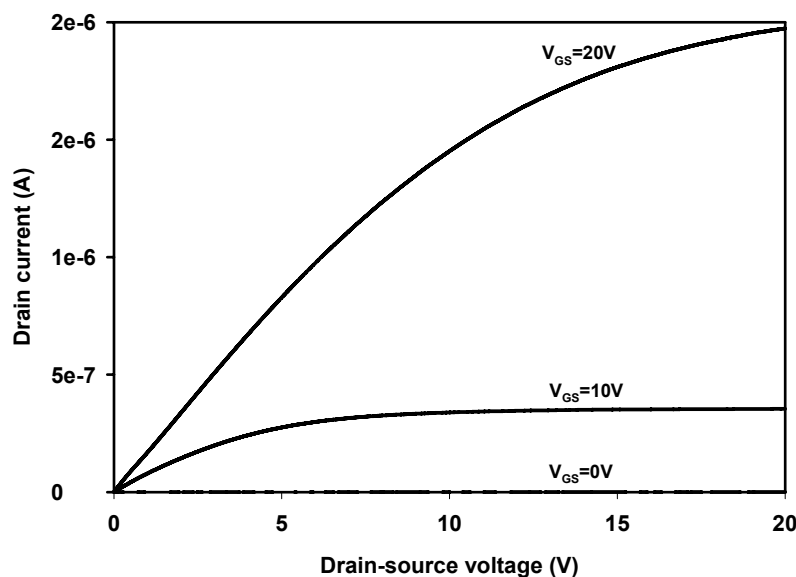
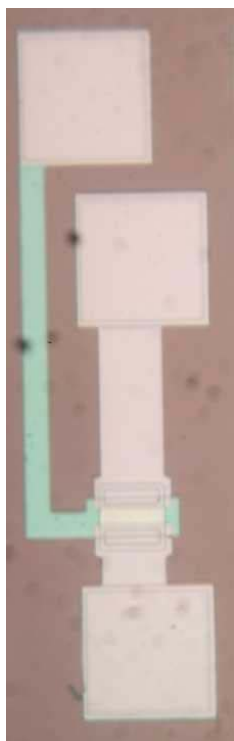
0.7 cm²/Vs

Threshold voltage

3.2 V

Sub-threshold slope

0.4 V/Dec



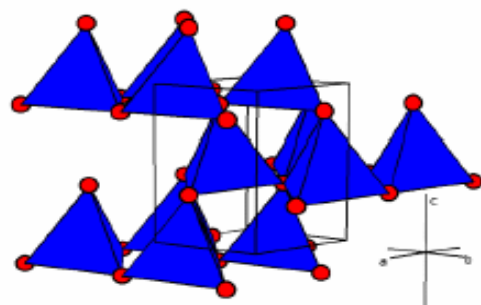
Deposition temperature 180 – 200 °C, possibly lower

Doped film resistivity as low as $3 \times 10^{-4} \Omega\text{-cm}$

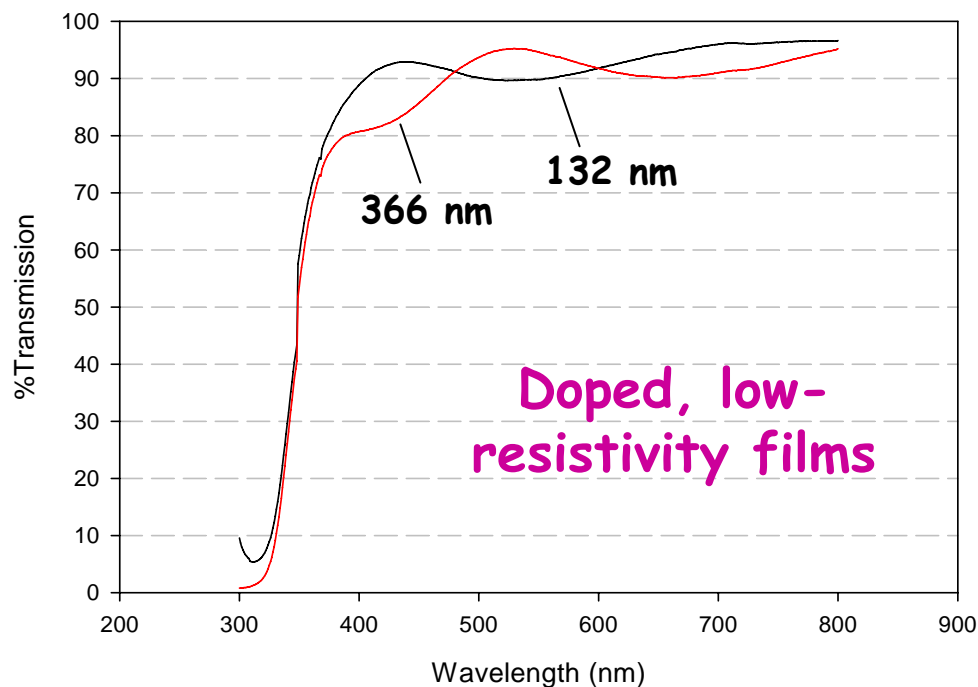
Doped film electron mobility $\sim 10 \text{ cm}^2/\text{V-s}$, undoped higher

Good transparency

Optical transmission

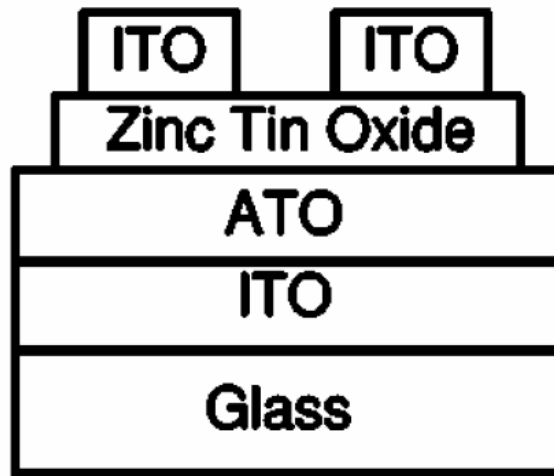


ZnO
Wurtzite ($P6_3mc$)
4-coordinate Zn^{2+}
4-coordinate O^{2-}
Corner Sharing



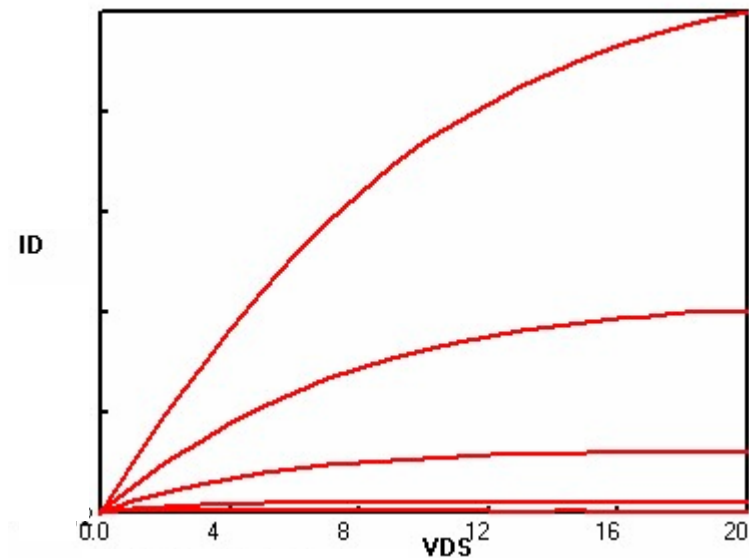
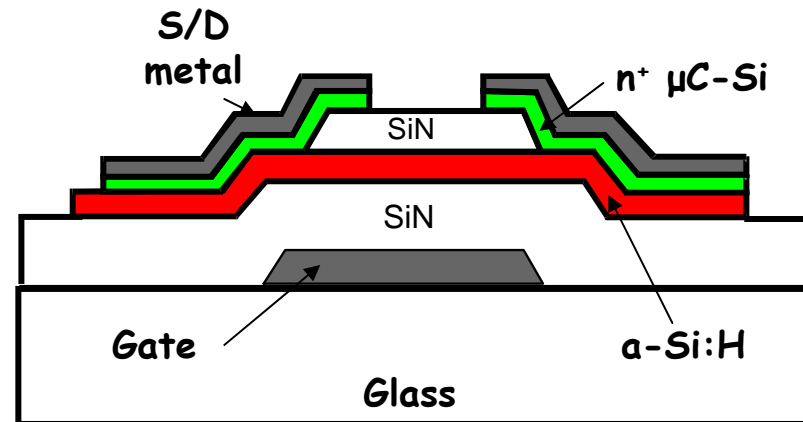


Most ZnO TFTs demonstrated to date have not used contact doping



Hoffman, et al
APL 86, 13503 (2005)

Doped contacts likely to improve TFT extrinsic mobility and off current



Low temperature polyester - organic TFTs

Revolutionary technology

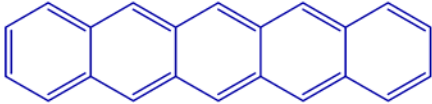
(some connections to $\$3 \times 10^9$ /year OLED "industry")

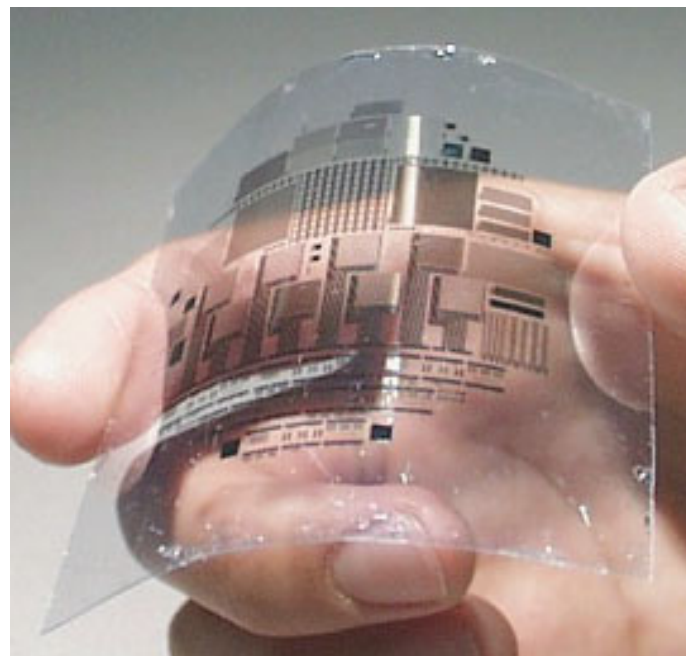
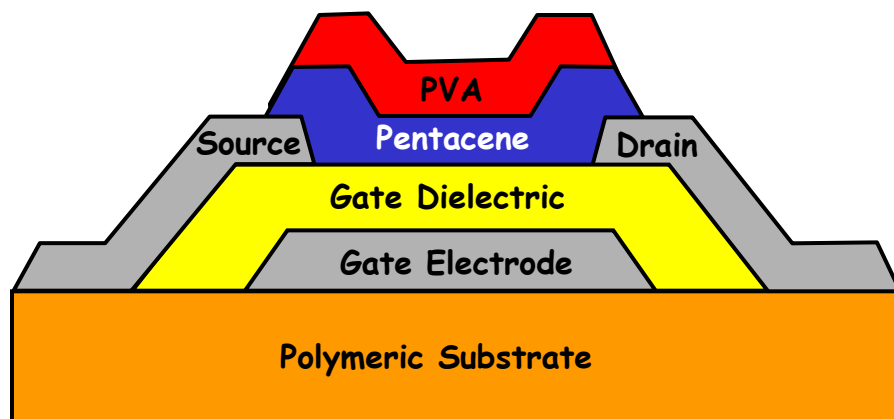


Small Molecule Organic Semiconductors

- Low temperature processing allows arbitrary substrates and flexible processing
- Simple device fabrication

Pentacene:

-  **pentacene**
- Small molecule organic semiconductor
- Thin film mobility $> 3 \text{ cm}^2/\text{V-s}$, $\sim 1 \text{ cm}^2/\text{V-s}$ typical
- Simple low-temperature vacuum deposition
- Strong tendency to form well-ordered molecular crystals

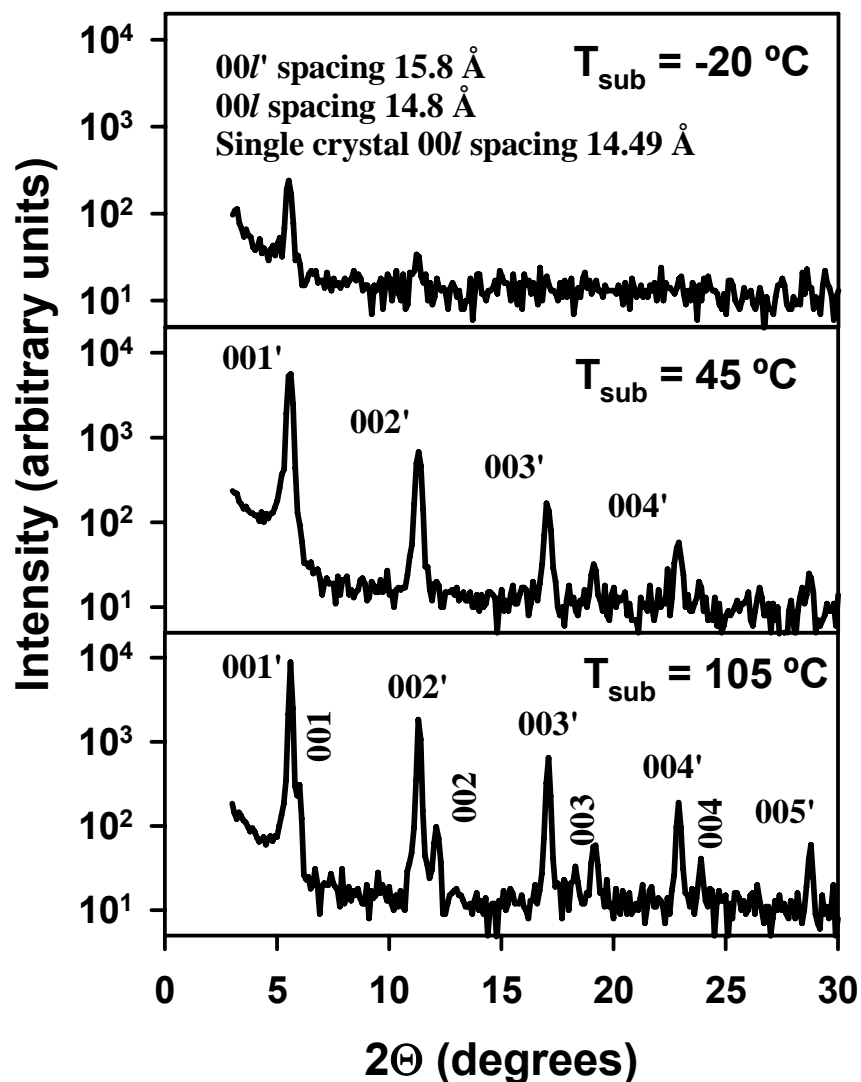




x-ray diffraction

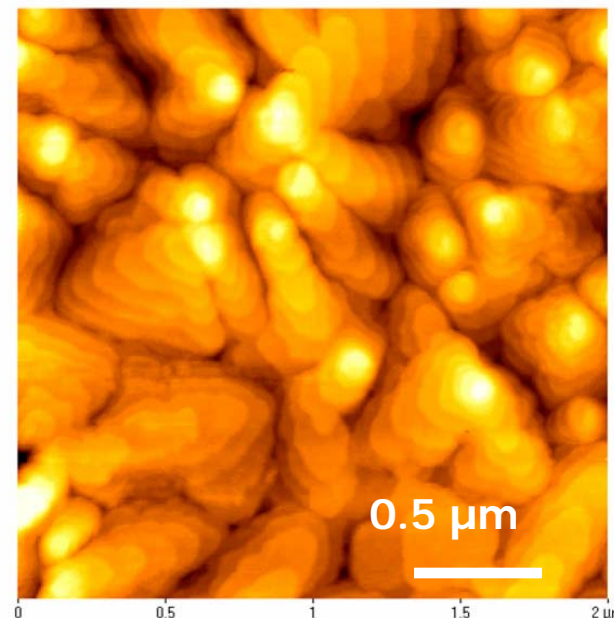
500 Å Pentacene films

- Molecular self-assembly
- Films ordered at low temperature
- Islands of electron density

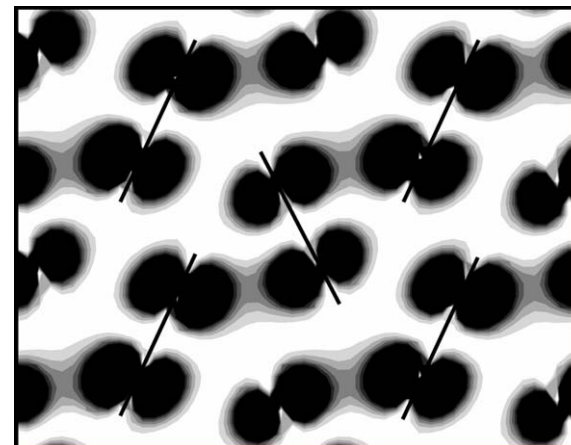


AFM shows
strong
molecular
terracing

$T_{\text{sub}} = 30^\circ\text{C}$

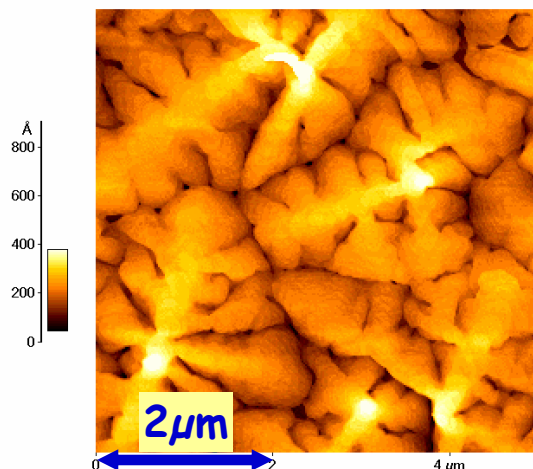


Homo electron
density, looking
along c-axis
(K. Hummer, P.
Puschig, C. Ambrosch-Draxl *Electronic
Properties of Oligo-
Acenes*, April 2003,
Vienna, Austria)

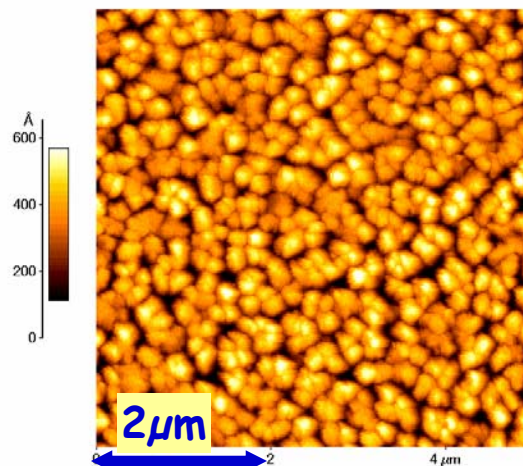




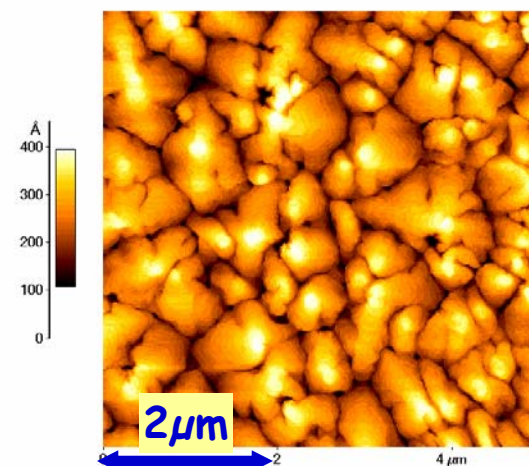
Surface roughness



Thermal SiO₂
~ 1 Å rms roughness



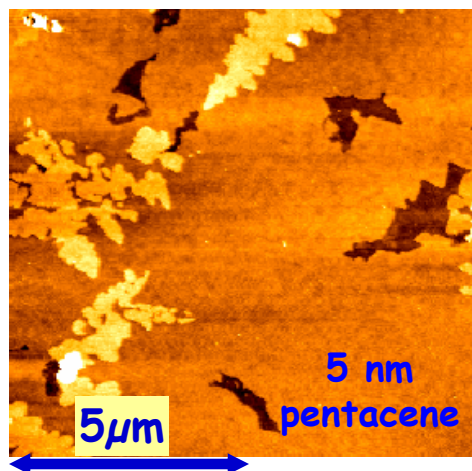
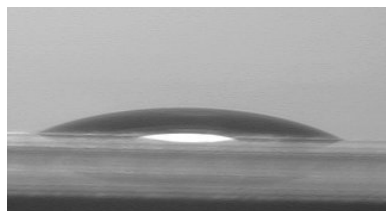
Evaporated Au
~ 5 Å rms roughness



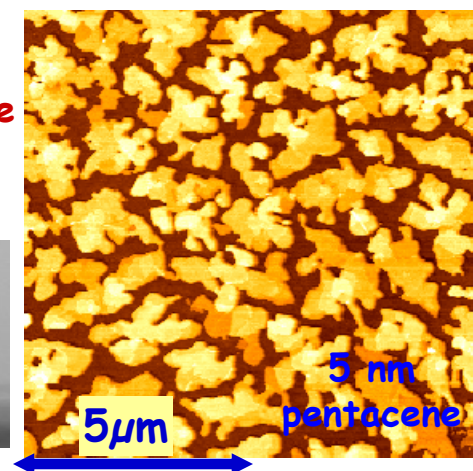
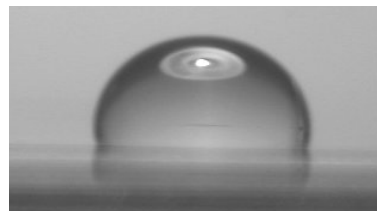
Ion beam sputtered Pd
~ 2 Å rms roughness

Surface energy

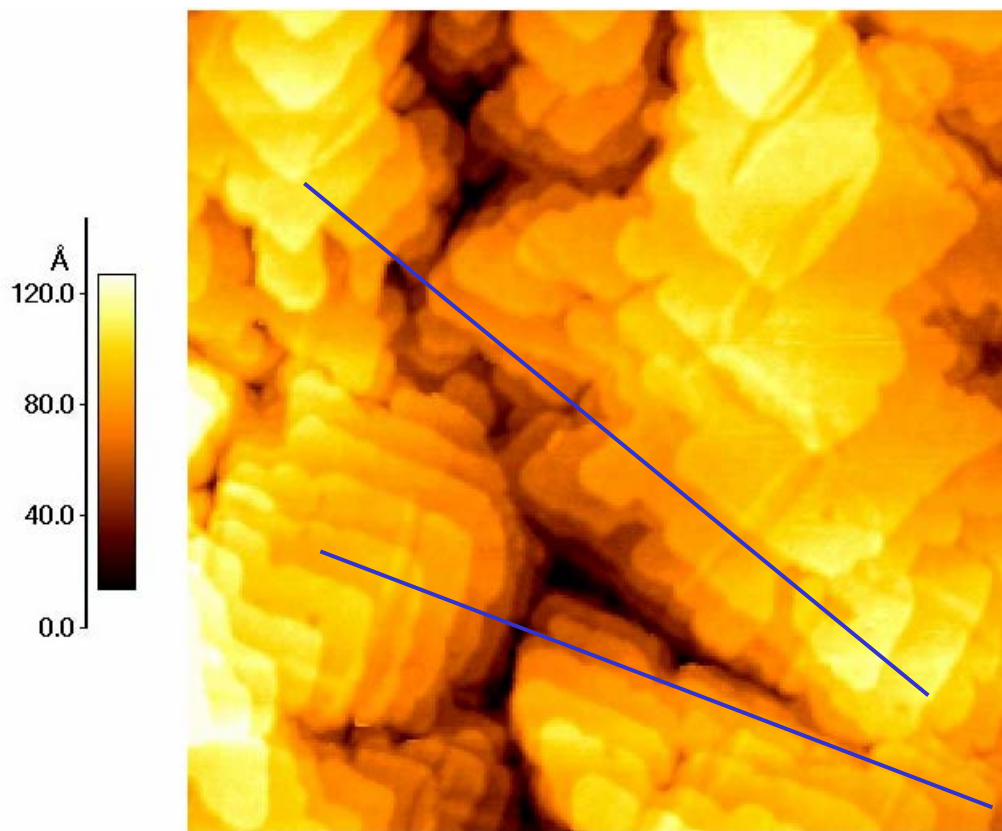
untreated SiO₂
high surface energy



SiO₂ treated with octadecyltrichlorosilane (OTS)
low surface energy



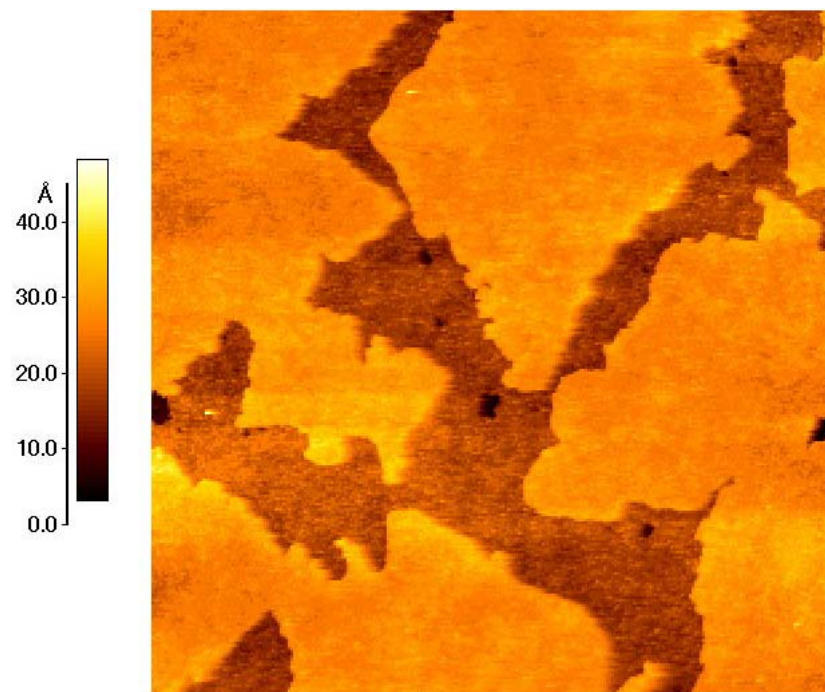
Facet directions are often coherent
across apparent grain boundaries



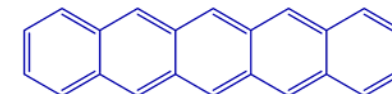
30 nm average thickness

No clear correlation between grain
boundary density and OTFT performance

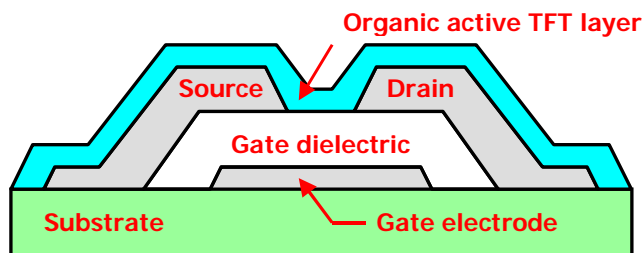
Connection of topography
to microstructure and
transport not clear



5 nm average thickness

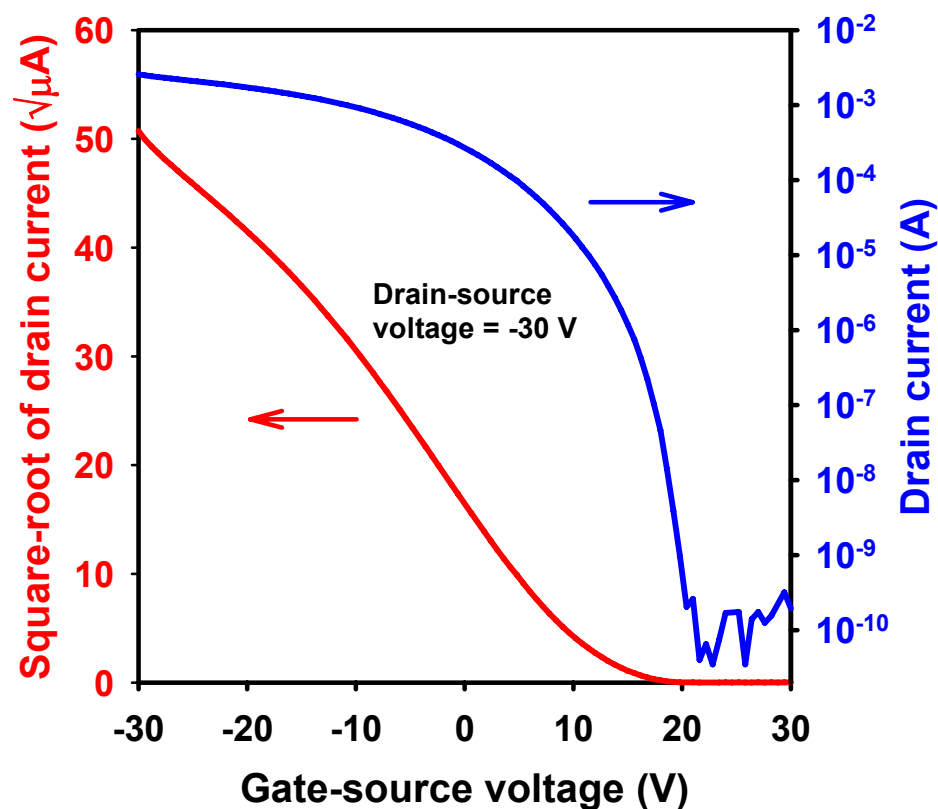
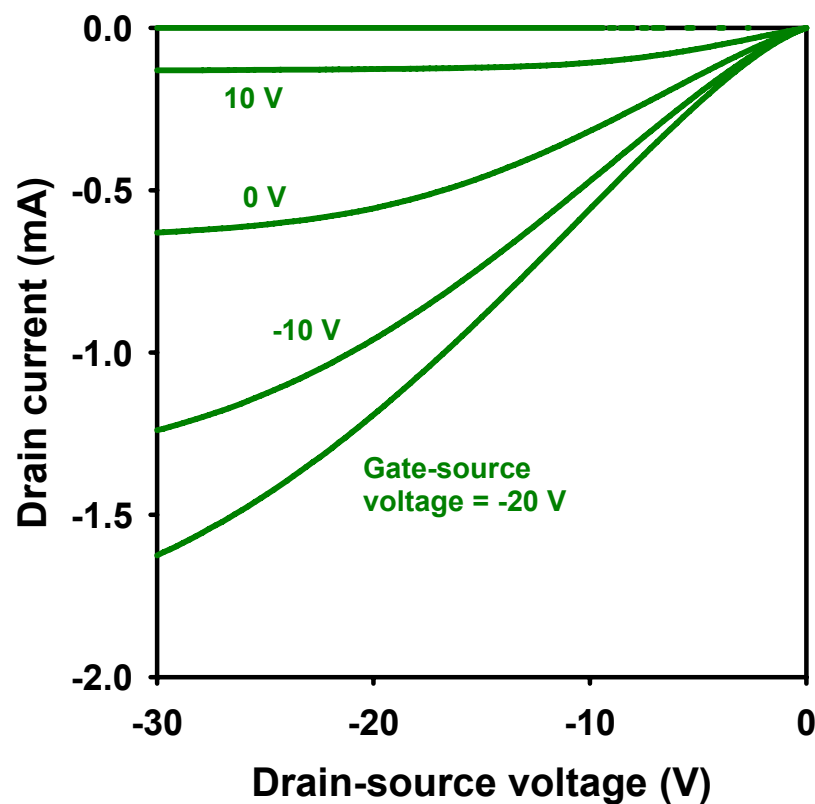


Hard substrate (glass or silicon) devices



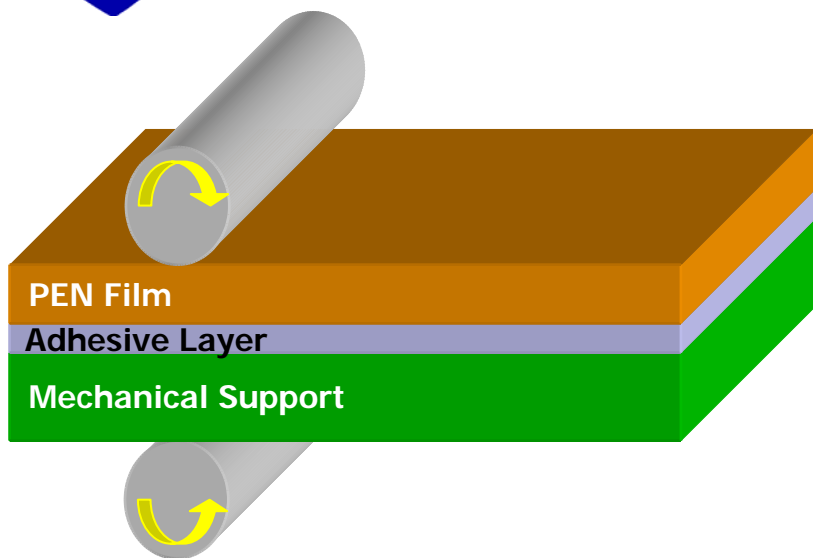
$$W / L = 500 \mu\text{m} / 5 \mu\text{m}, \quad t_{\text{ox}} = 150 \text{ nm}$$

$$\mu = 1.7 \text{ cm}^2/\text{V-s}, \quad I_{\text{on}} / I_{\text{off}} = 10^8, \quad S = 0.9 \text{ V/dec}$$

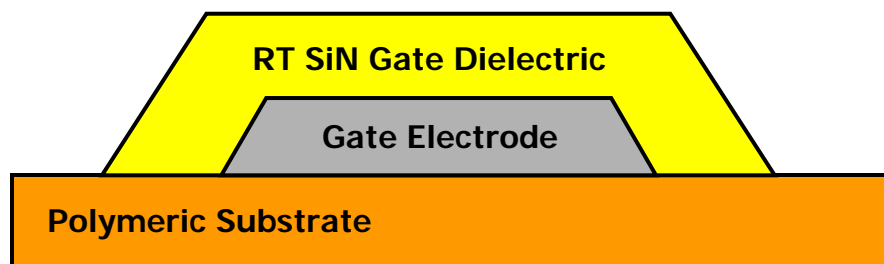




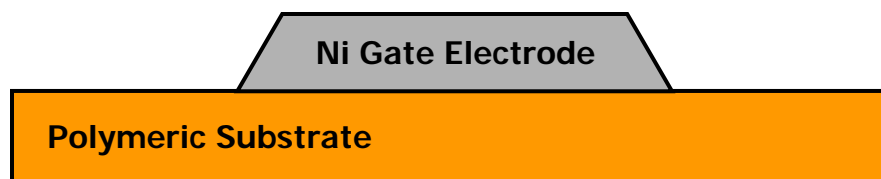
Polymeric Substrate OTFT Process



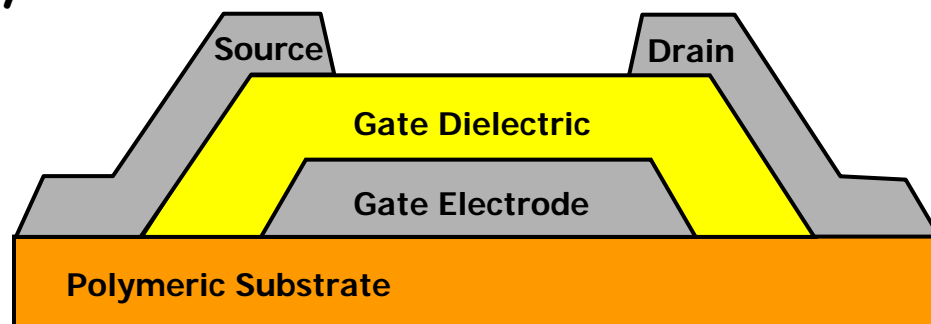
Polymeric film mounted to support,
preshrink to improve thermal stability



Room-temperature PECVD
SiN deposited and patterned



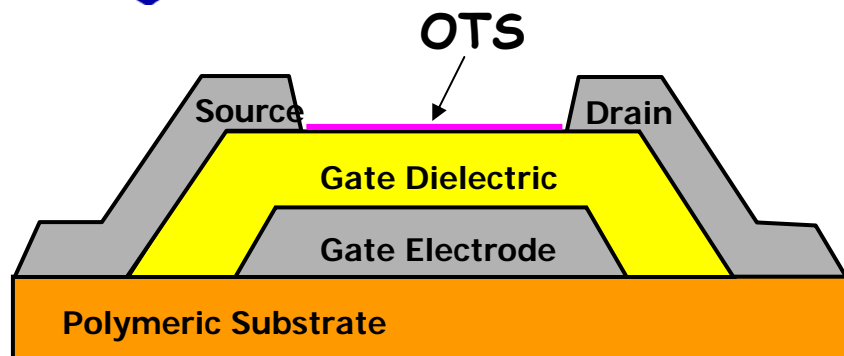
Ni gate electrode
deposited and patterned



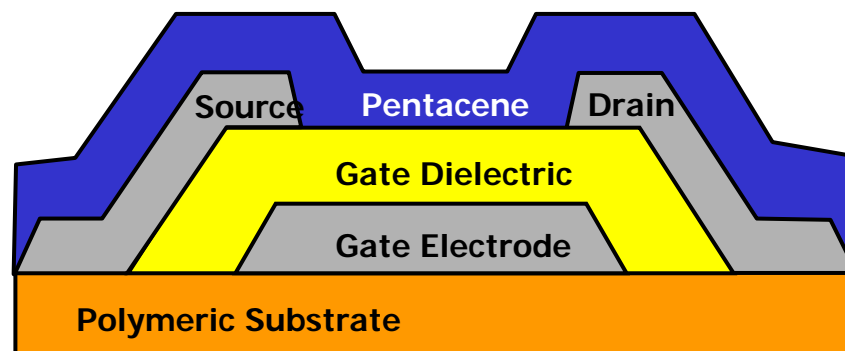
Pd source and drain electrodes
deposited and patterned



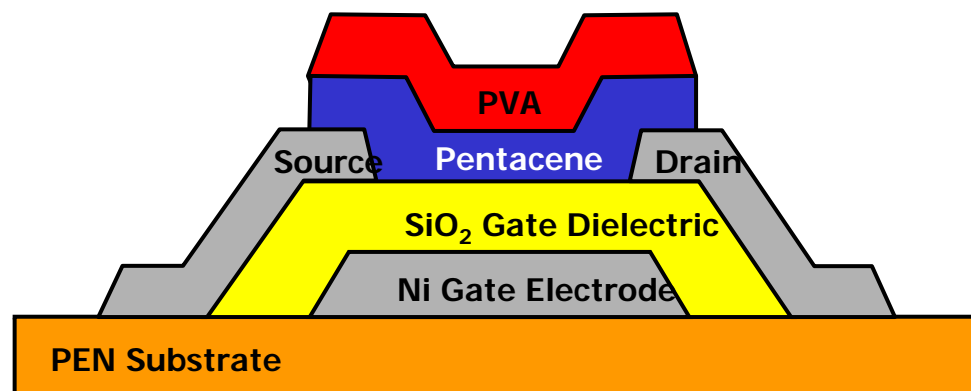
Polymeric Substrate OTFT Process



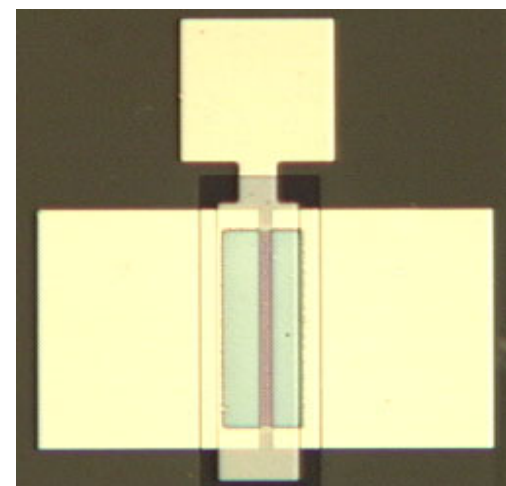
SCA (octadecyltrichlorosilane) treatment



Pentacene active layer deposited



Pentacene patterned using water-based photoresist and plasma etching



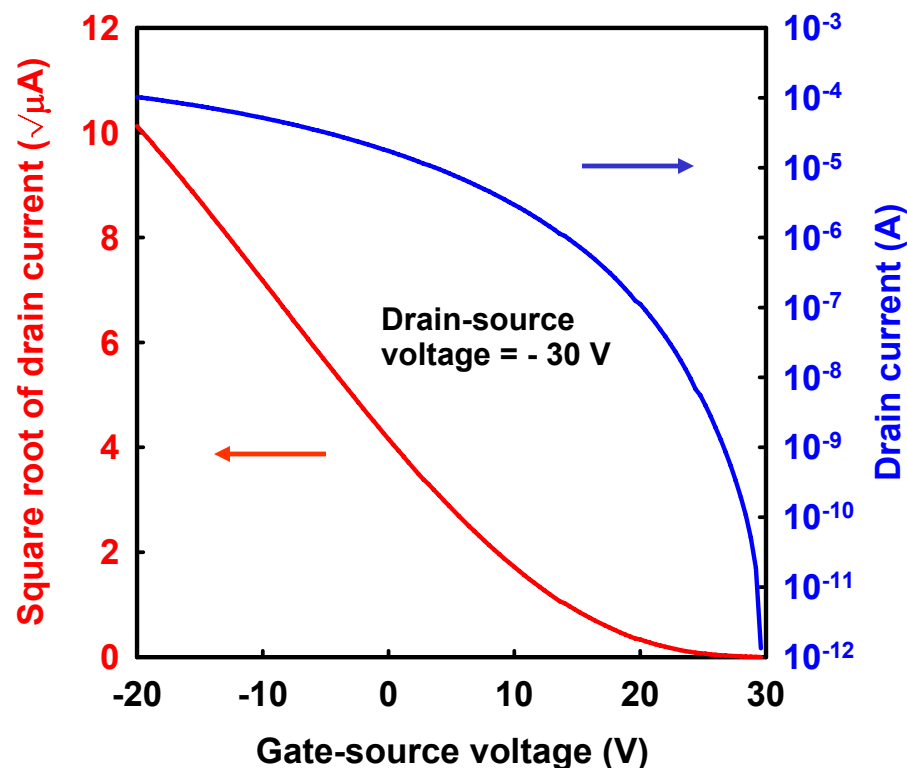
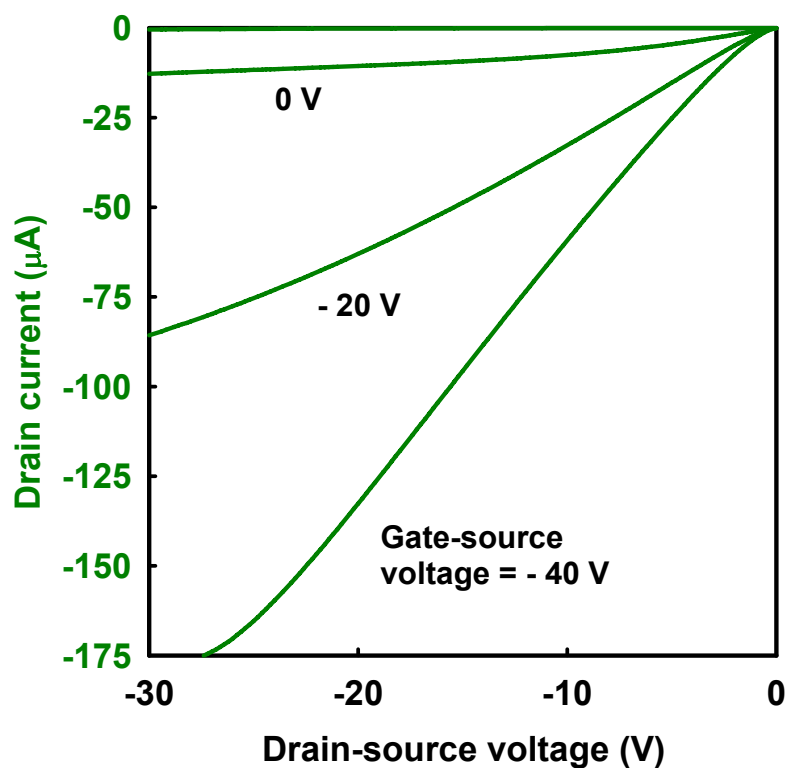
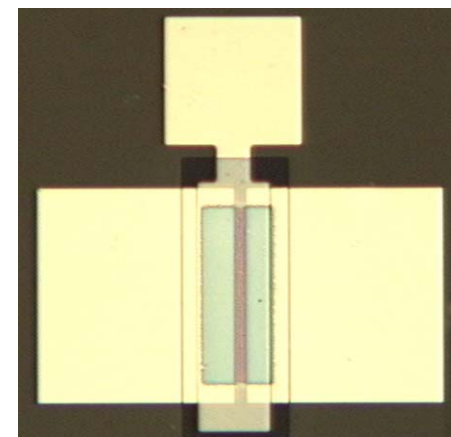
Completed discrete device



Discrete TFT Characteristics

$$W / L = 200 \mu\text{m} / 10 \mu\text{m}, \quad t_{\text{ox}} = 450 \text{ nm}$$

$$\mu = 1.2 \text{ cm}^2/\text{V-s}, \quad I_{\text{on}} / I_{\text{off}} = 10^8$$

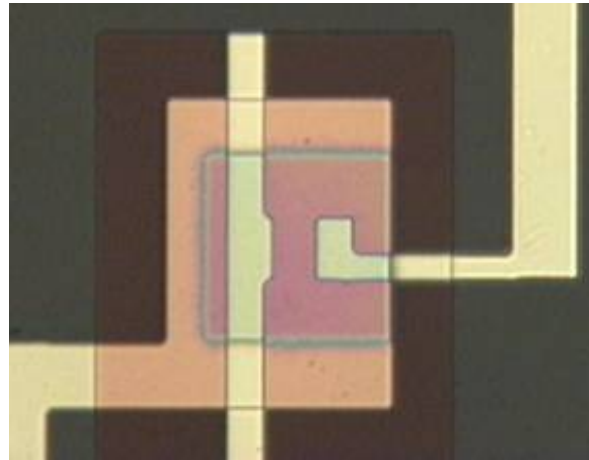




Statistics for 1 cm² 200 transistor array

$$W = 25 \mu\text{m}$$

$$L = 20 \mu\text{m}$$



Mobility

$$\text{average } \mu = 0.81 \text{ cm}^2/\text{V-s}$$

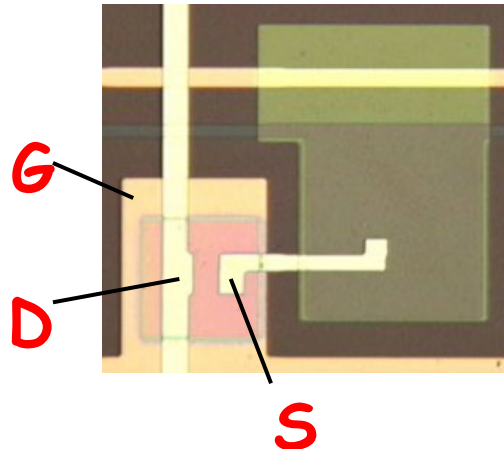
$$\sigma_{\mu} = 0.05 \text{ cm}^2/\text{V-s}$$

$$\text{for } V_{DS} = -20 \text{ V}$$

Threshold voltage

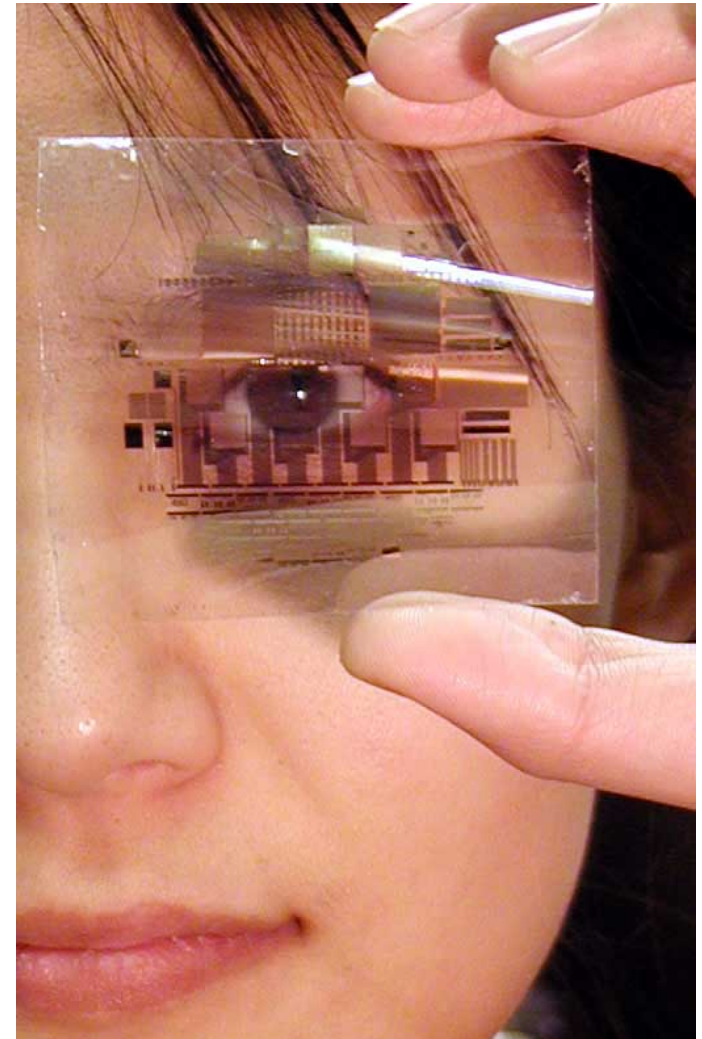
$$\text{average } V_t = +1.8 \text{ V}$$

$$\sigma_{V_t} = 0.8 \text{ V}$$



On/off current ratio

$$10^6 \dots 10^7$$



Collaboration with [SARNOFF](#)



Active electronics
will drive yield

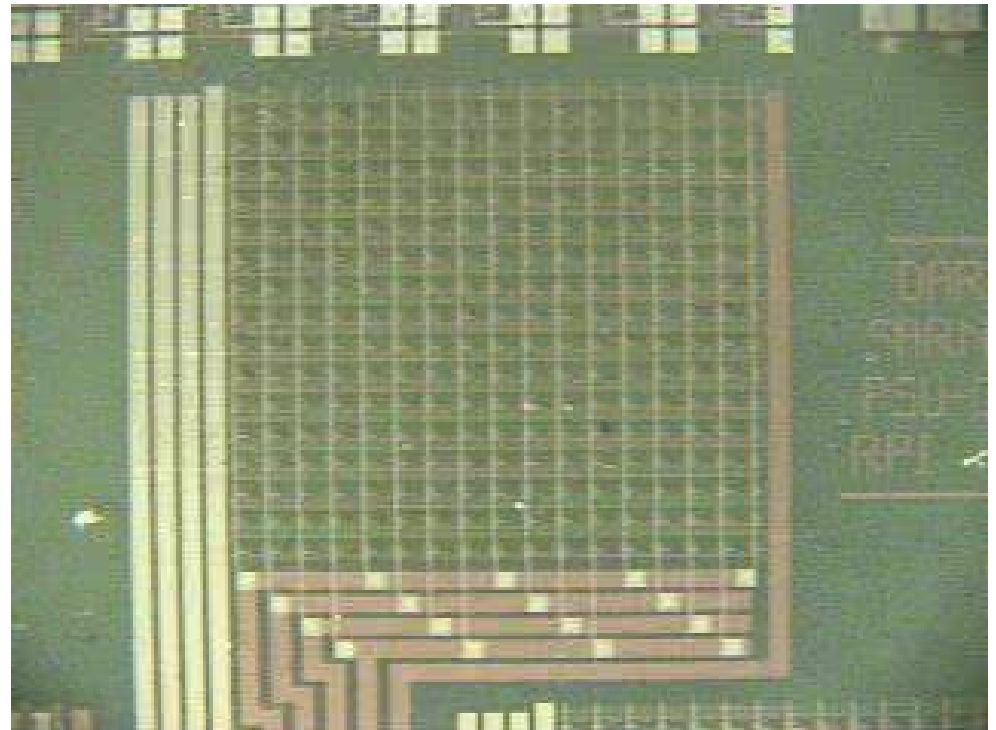
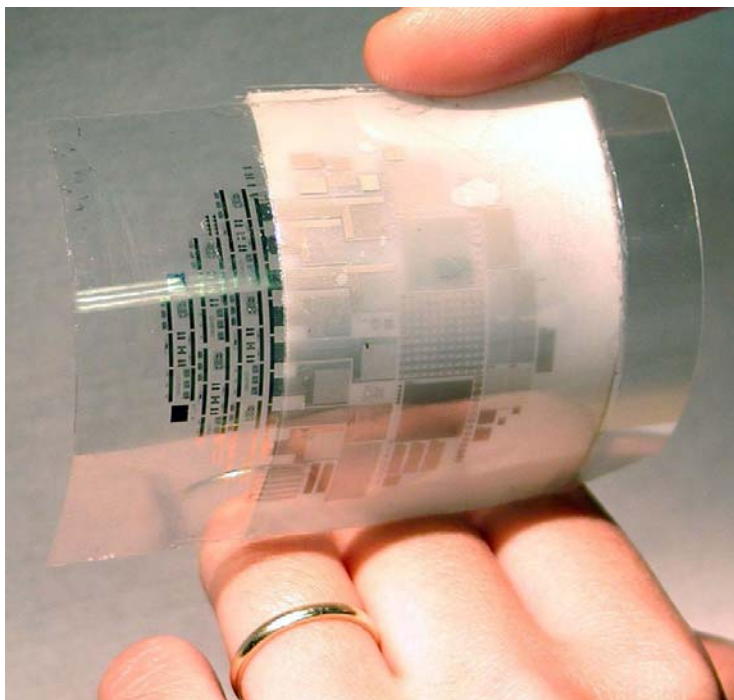
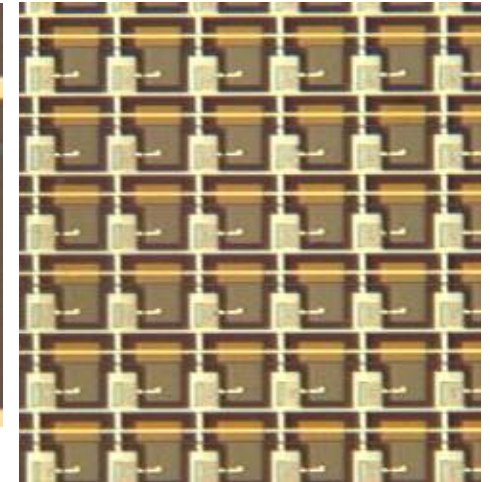
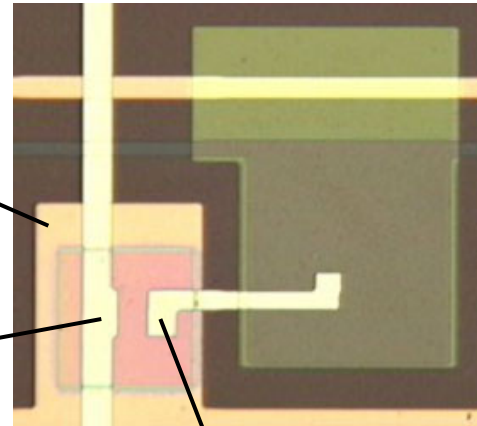
Organic TFT polymer dispersed LC display

- Simple repeating 4 x 4 layout
- $\frac{1}{4}$ VGA drive conditions (1/4 VGA):
69 μ sec line time
60 Hz refresh rate
- Illumination 45°; black absorber

G

D

S



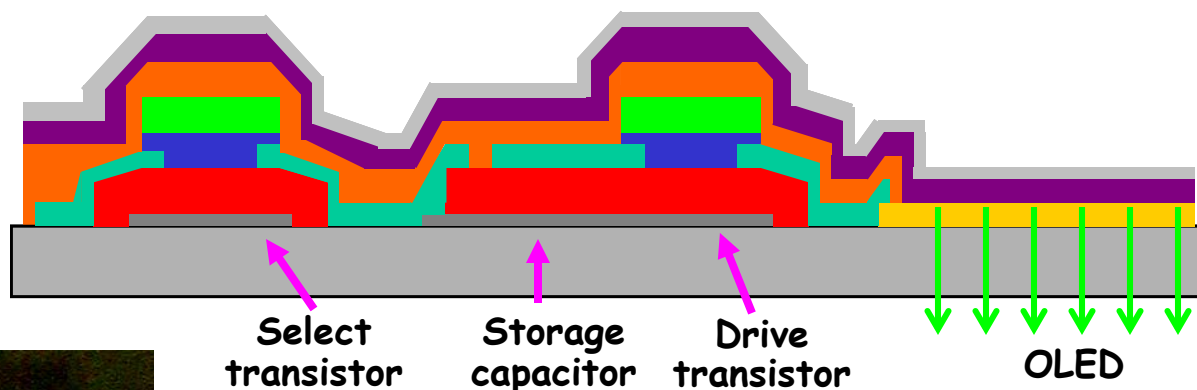


OTFT/OLED Active Matrix Display

Gate	ITO	Pentacene	Passivation
Oxide	S/D	Isolation	OLED
			Cathode

Photosensitive polyvinyl alcohol used for OTFT patterning and isolation

Parylene used to separate OTFTs and OLEDs

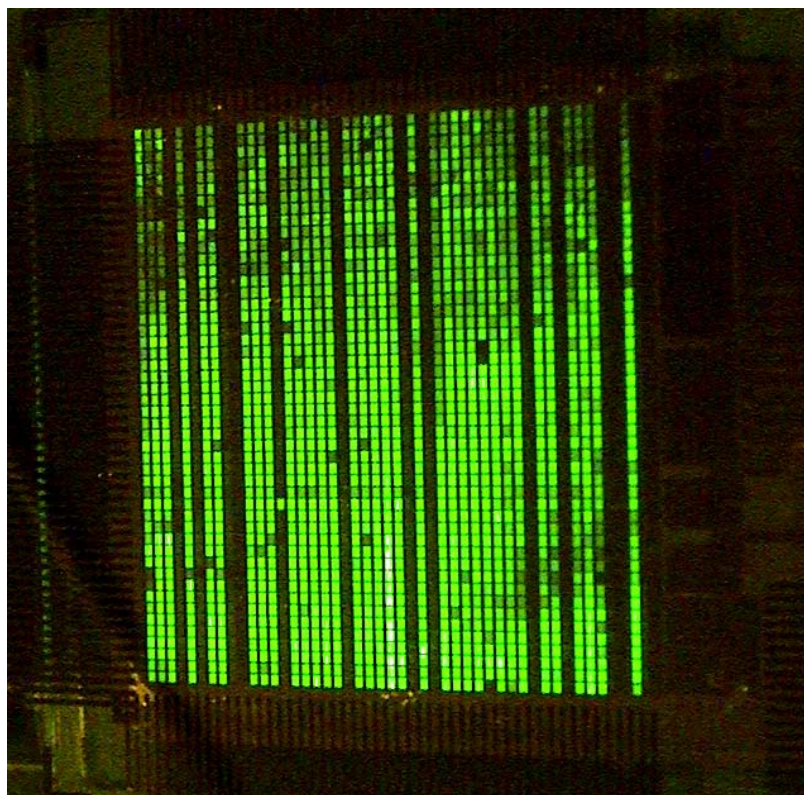


Select transistor

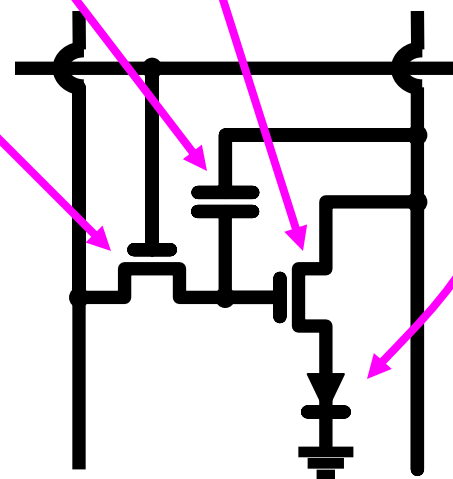
Storage capacitor

Drive transistor

OLED



48 x 48 pixel array on glass



Simple two-transistor per pixel design



100 OTFT Array Uniformity Test

$W/L=200/20\mu\text{m}$

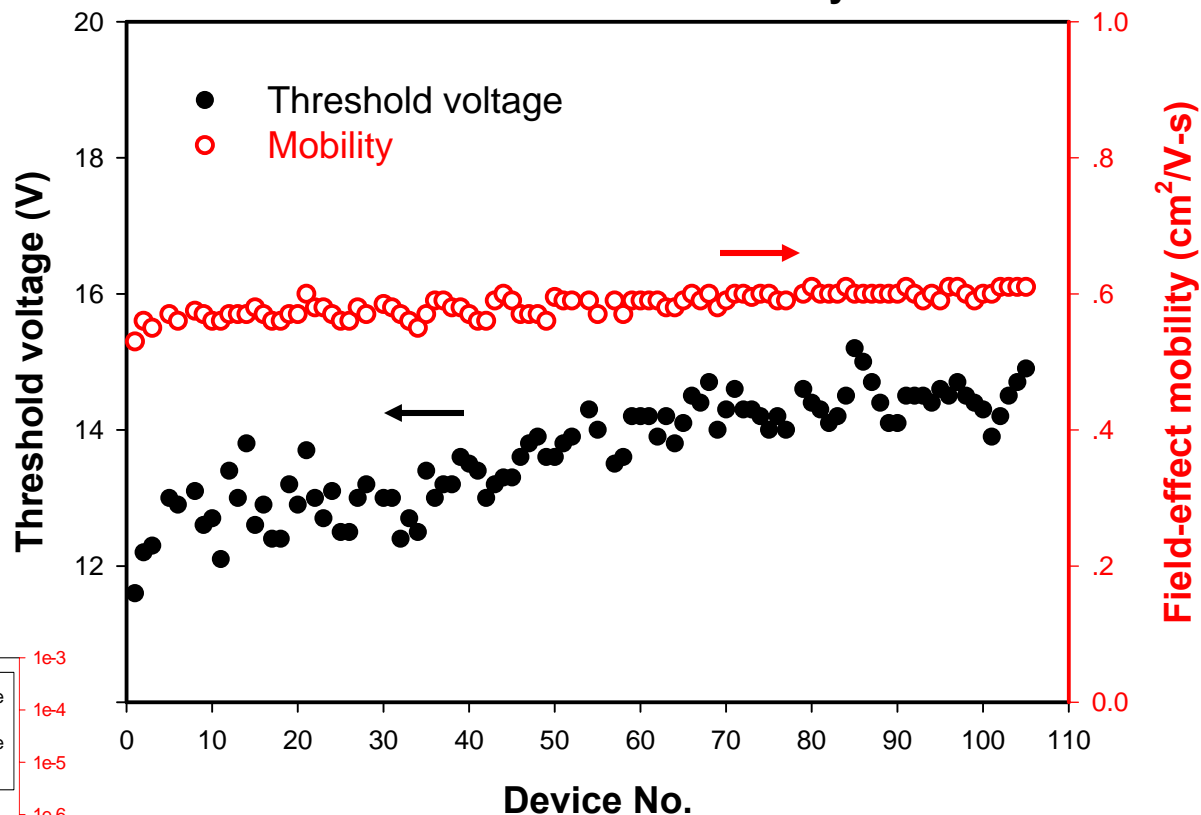
$T_{\text{OX}}=300\text{nm}$

Pt S/D bottom contact

PVA patterned pentacene

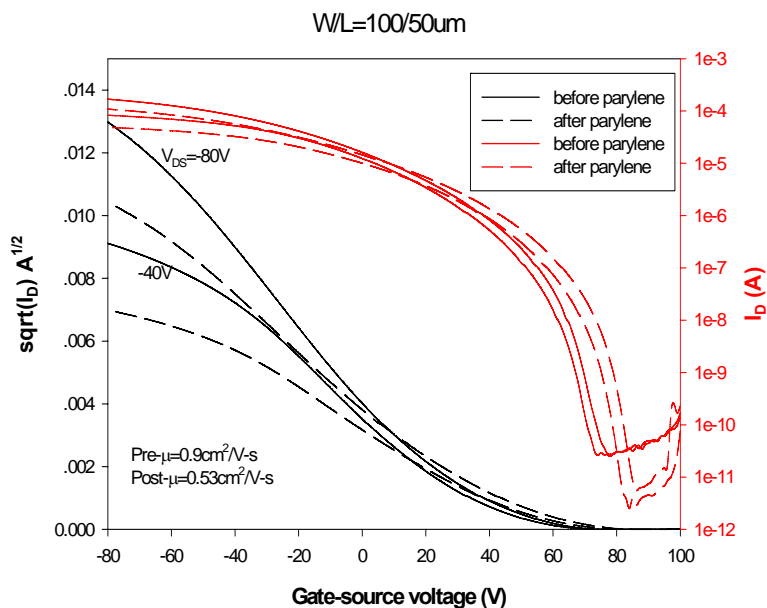
Parylene passivation

LM #9: Test of TFT Uniformity



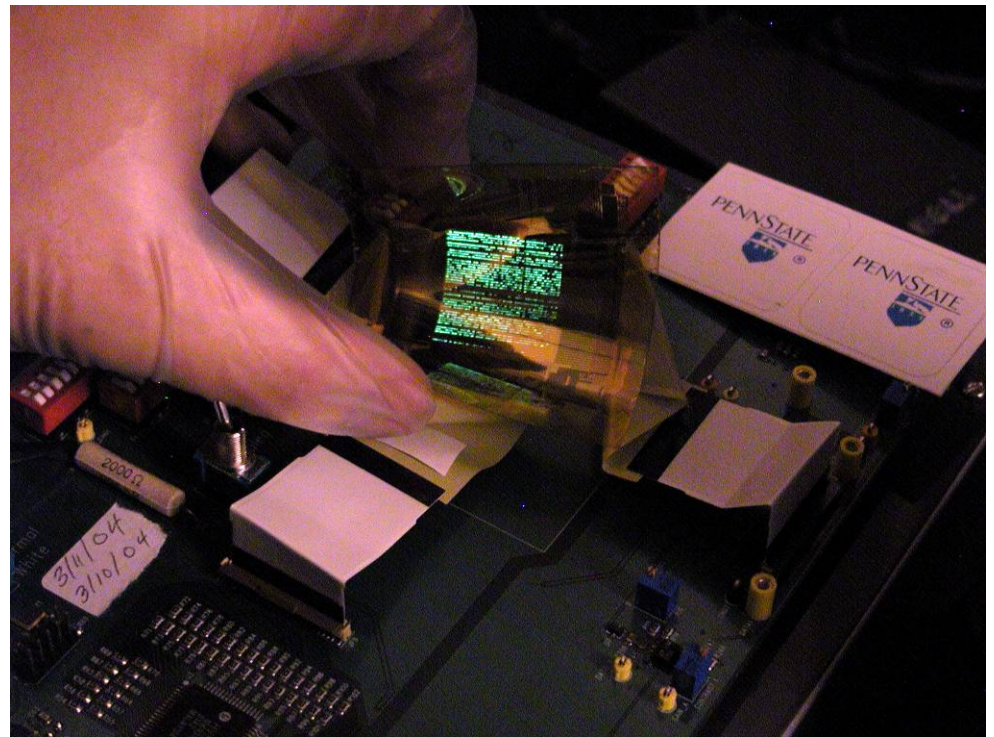
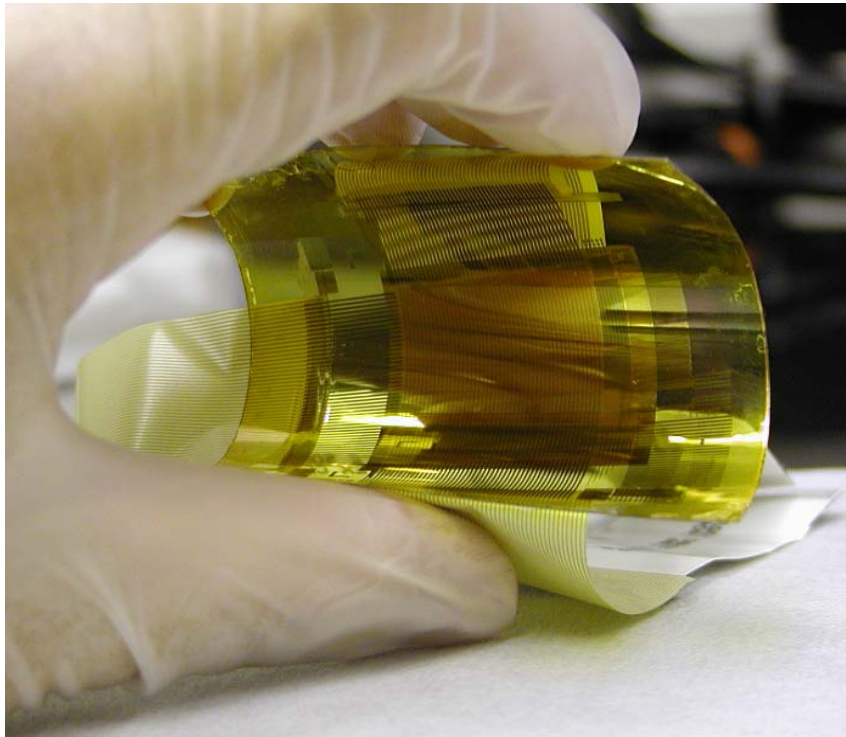
Average mobility = $0.584 \text{ cm}^2/\text{Vs}$
 $\sigma = 0.017 \text{ cm}^2/\text{Vs}$

Average threshold voltage = 13.7 V
 $\sigma = 0.78 \text{ V}$



Flexible Substrate OTFT/OLED Active Matrix Display

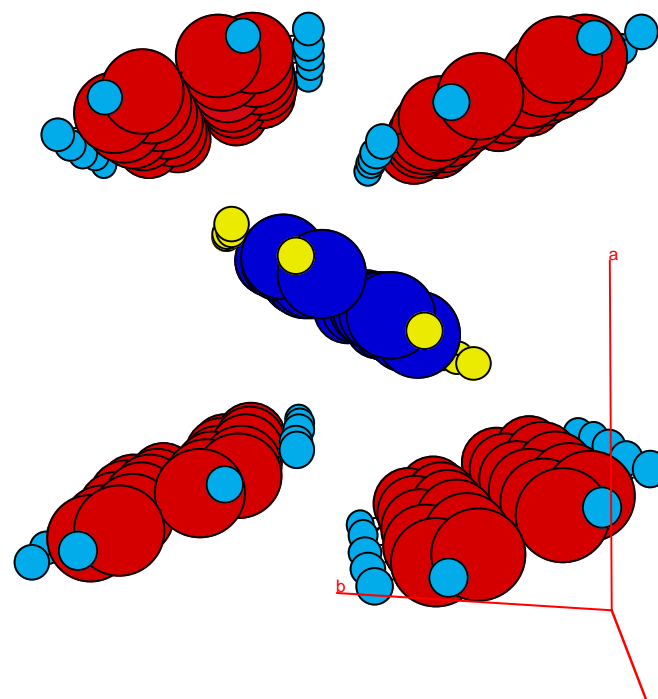
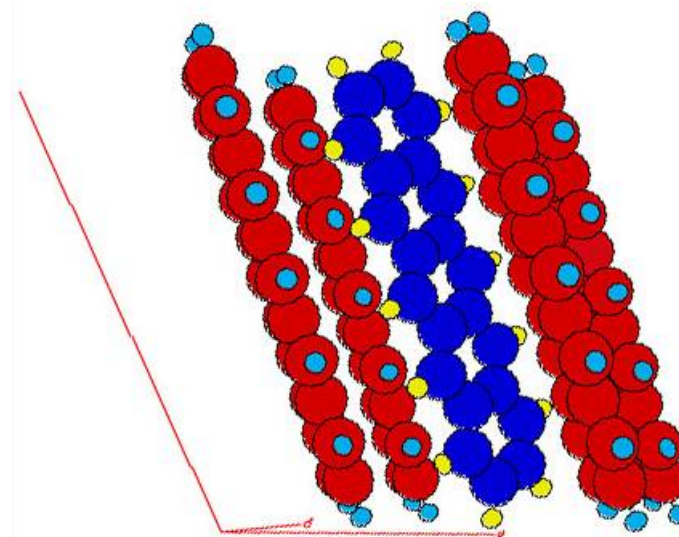
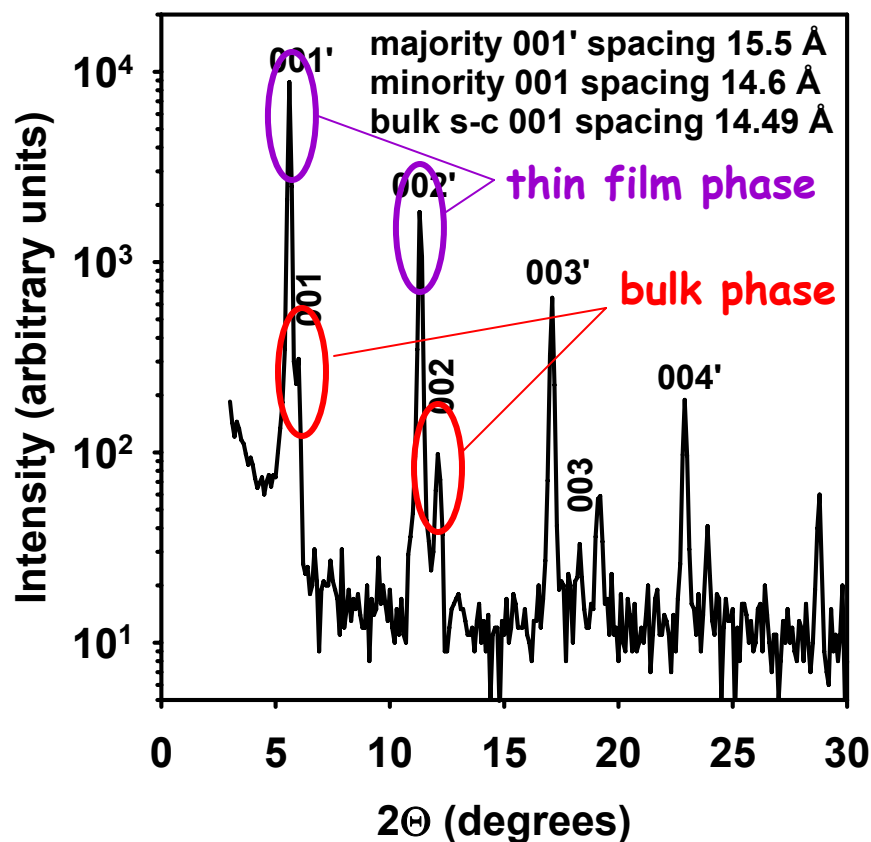
- PET substrate
- Pentacene OTFT backplane
- Parylene passivation
- TPD/AIQ₃ OLEDs





Small-molecule semiconductors
are typically weakly bonded
molecular crystals

In pentacene this leads to a combination
of face-to-face and edge-to-face
interactions \Rightarrow minimal π -orbital overlap
& poor electronic transport

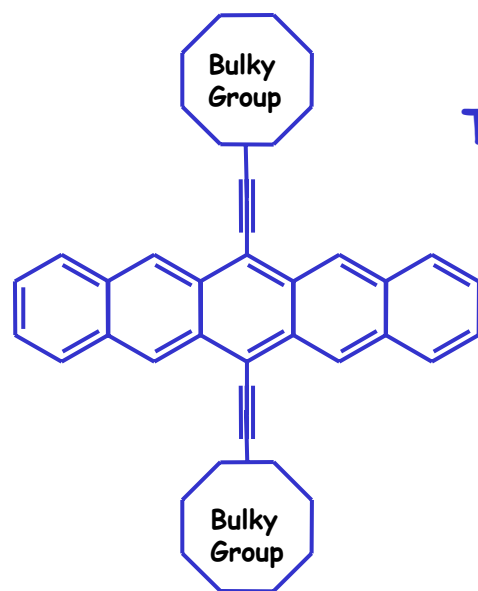
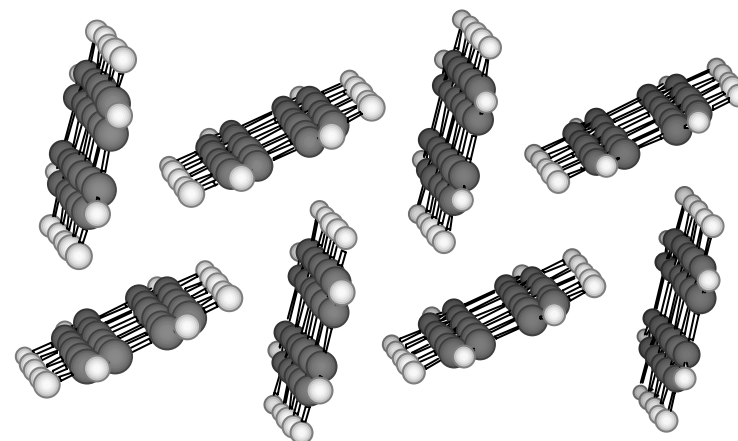
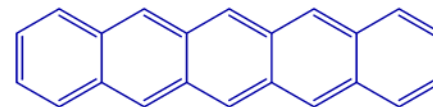




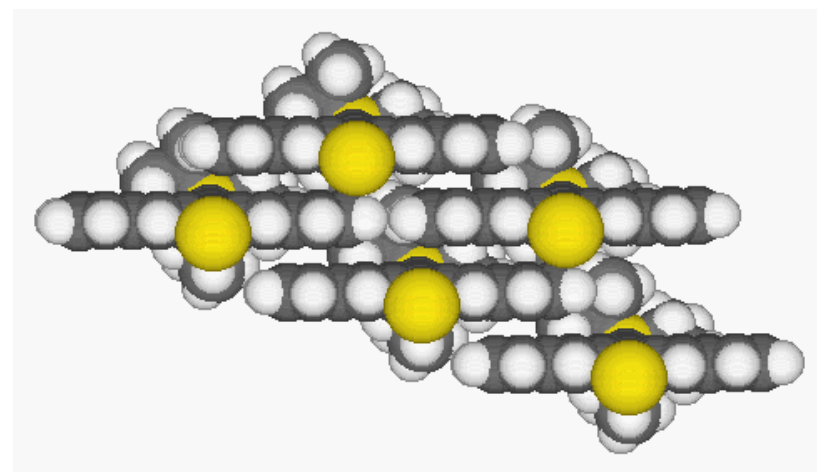
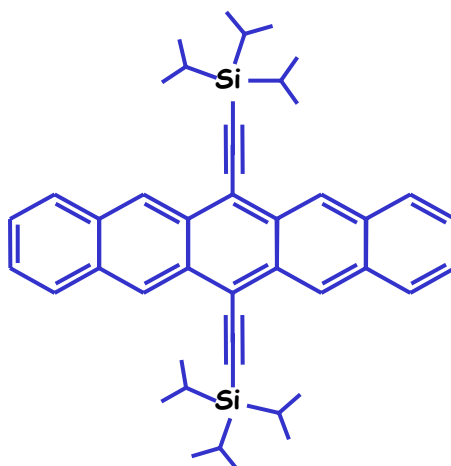
Pentacene derivatives

By substituting bulky groups at the 6,13 positions we can:

- Improve pi-orbital overlap
- Allow solution processing



Example:
Triisopropylsilylethynyl
(TIPS) pentacene



Collaboration
with J. Anthony

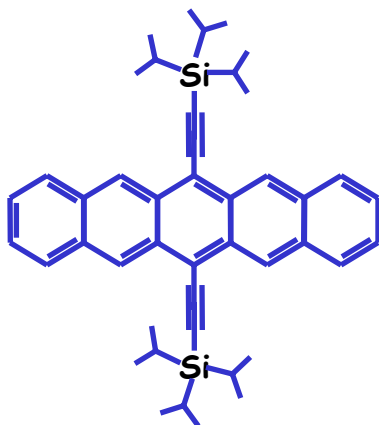


Best vapor deposited field-effect mobility $\sim 0.4 \text{ cm}^2/\text{V-s}$



Solution Processed TIPS Pentacene

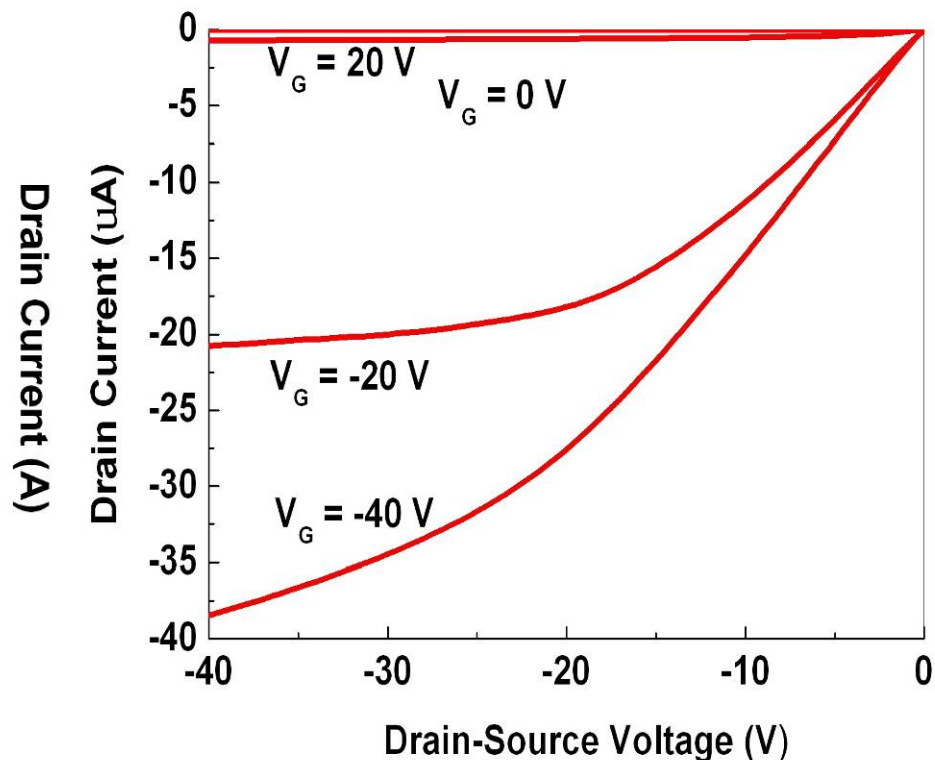
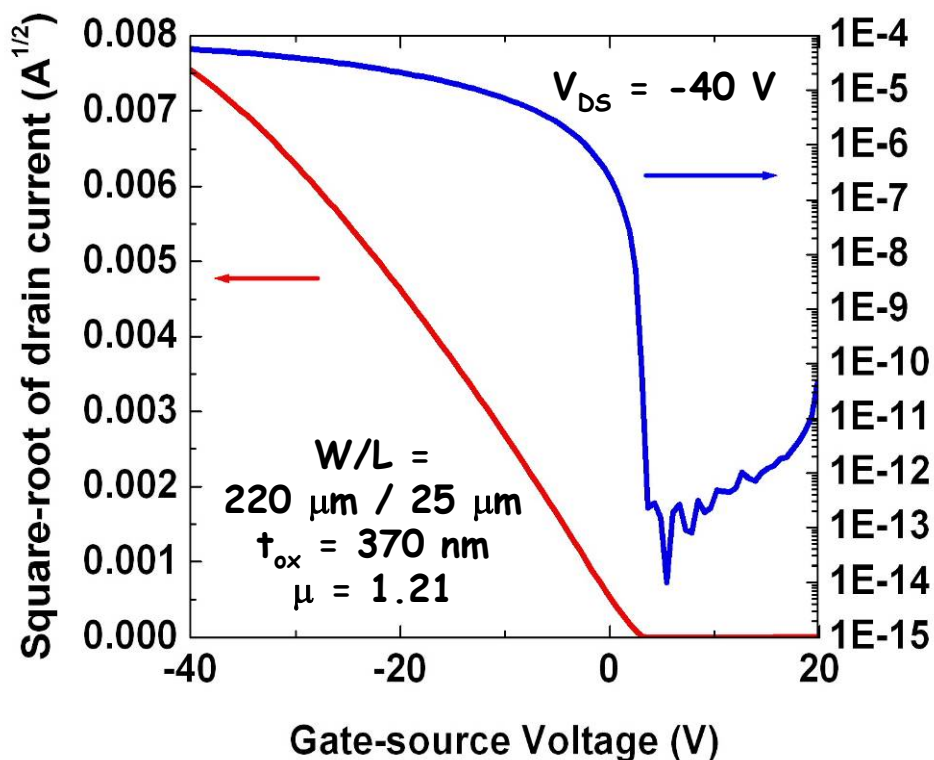
TIPS pentacene
(triisopropylsilyl
pentacene)

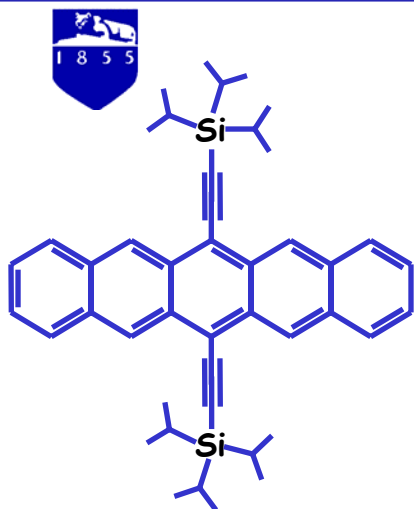


- Film thickness: 1000 ~ 5000 Å
- Drop cast from 1 wt% toluene solution
- HMDS dielectric treatment

$\mu = 0.23 \sim 1.5 \text{ cm}^2/\text{V}\cdot\text{s}$, $V_{th} = 0 \sim 5 \text{ V}$,
 $I_{on}/I_{off} = 10^7 \sim 8$, $S = 0.3 \sim 0.8 \text{ V/dec.}$

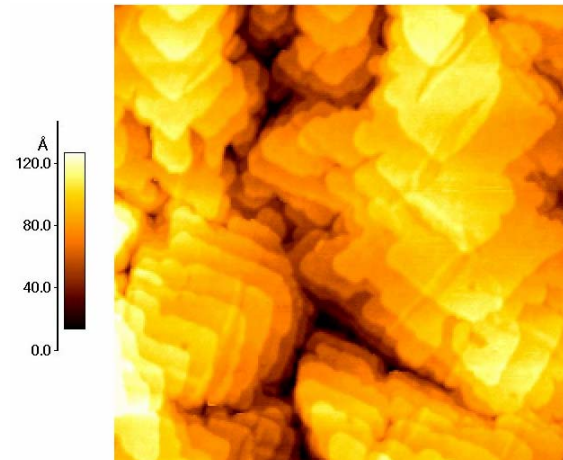
$\mu > 3 \text{ cm}^2/\text{V}\cdot\text{s}$ observed for a few devices





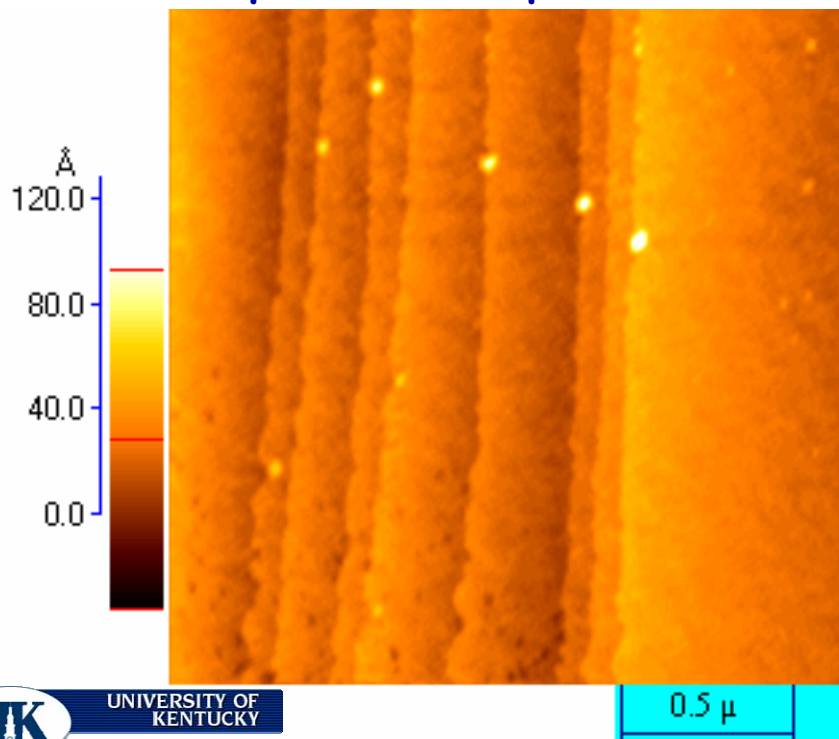
Molecular steps in drop-cast and spin-cast films

Solution deposited TIPS-pentacene films often have molecular ordering similar to vacuum deposited devices

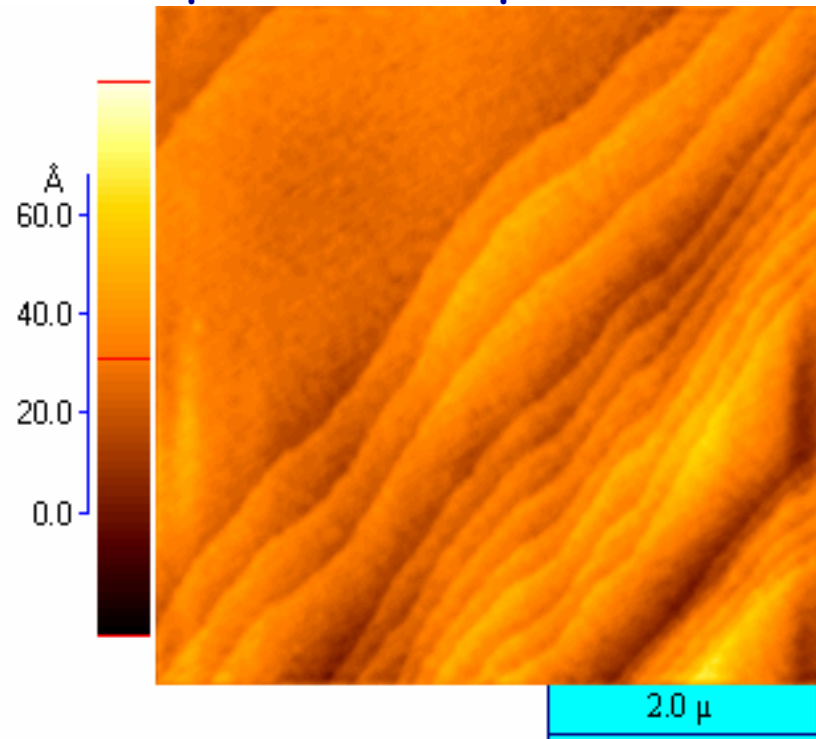


Evaporated pentacene

Drop cast TIPS-pentacene



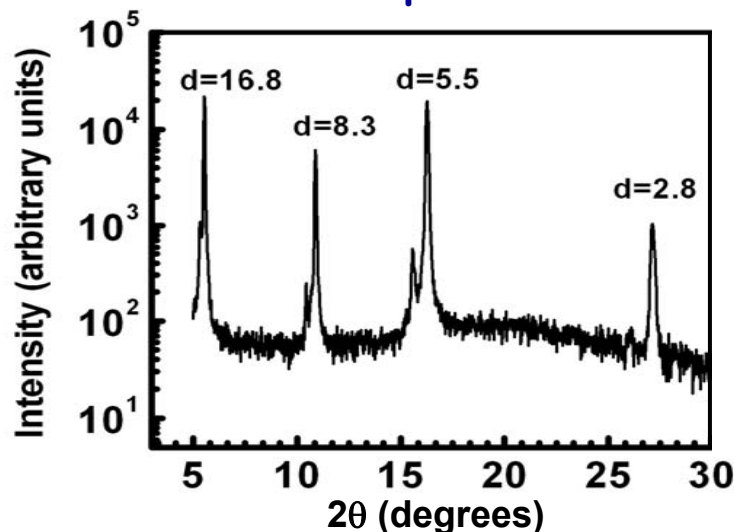
Spin cast TIPS-pentacene



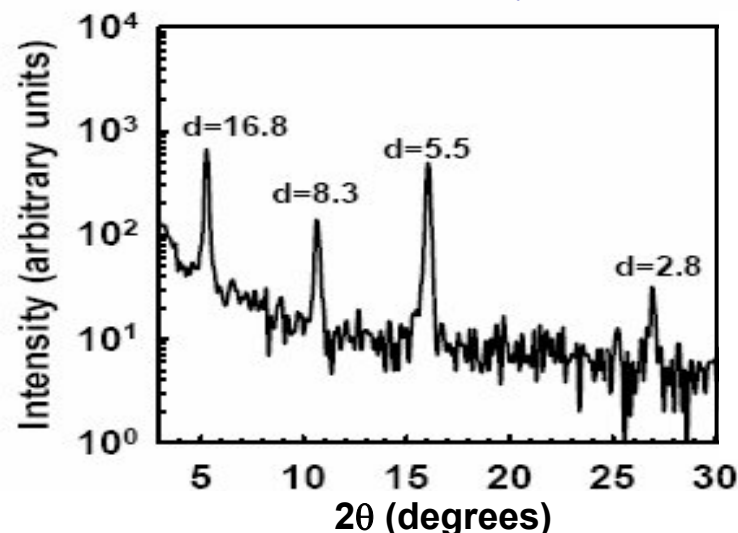
Molecular Ordering in Solution Deposited Films

X-ray diffraction for solution-deposited thin films very similar to single crystal

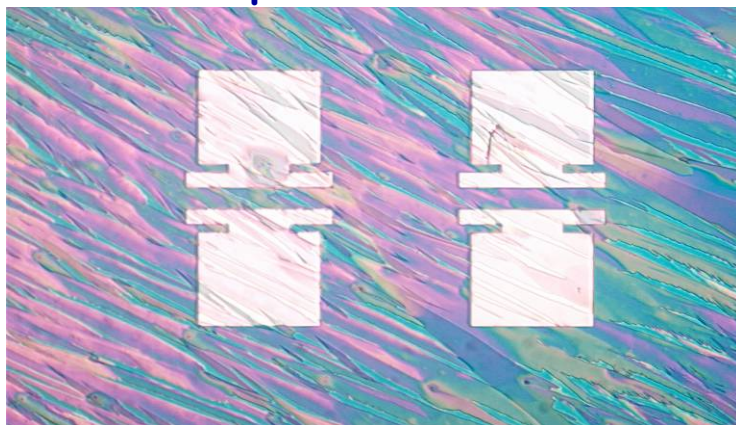
Solution-deposited TIPS



TIPS bulk crystal



Solution-deposited TIPS thin films



TIPS bulk crystal
(courtesy J. Anthony)

Macroscopic uniformity of solution deposited thin films fair to poor

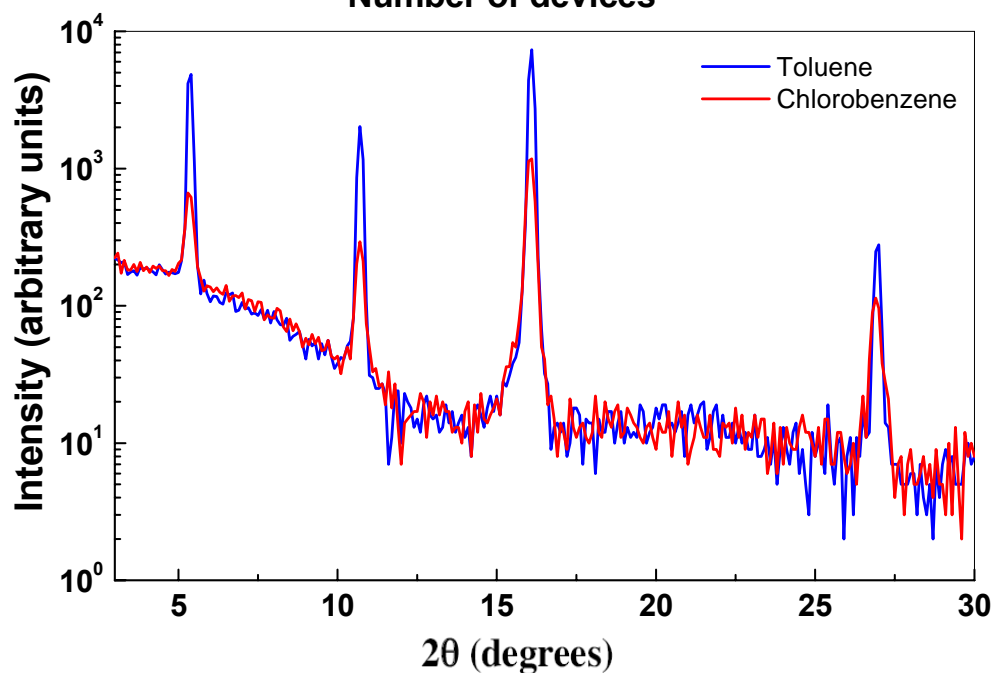
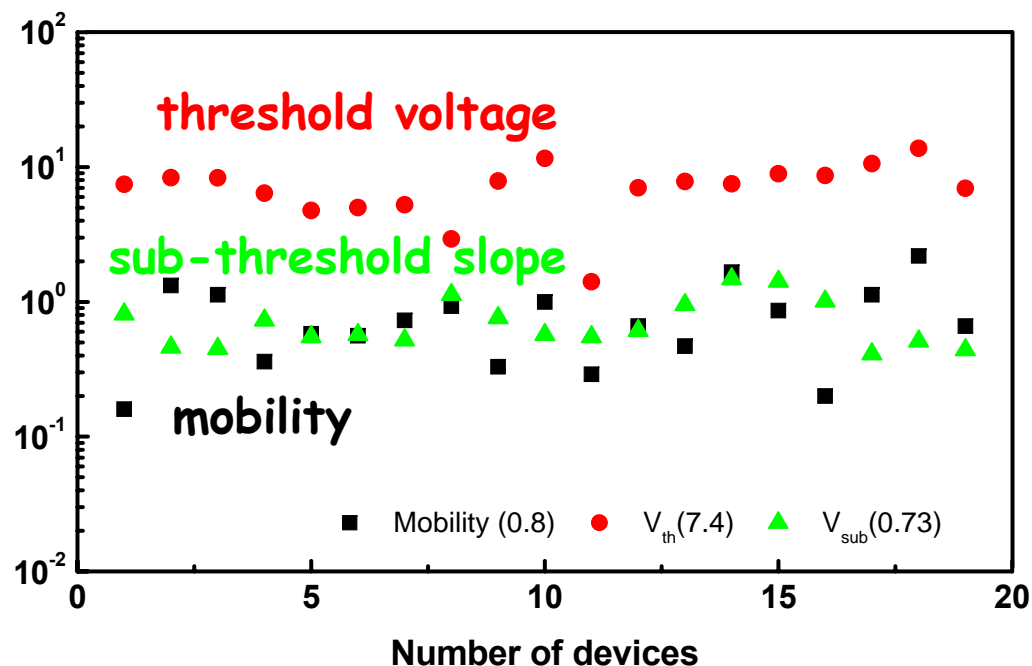


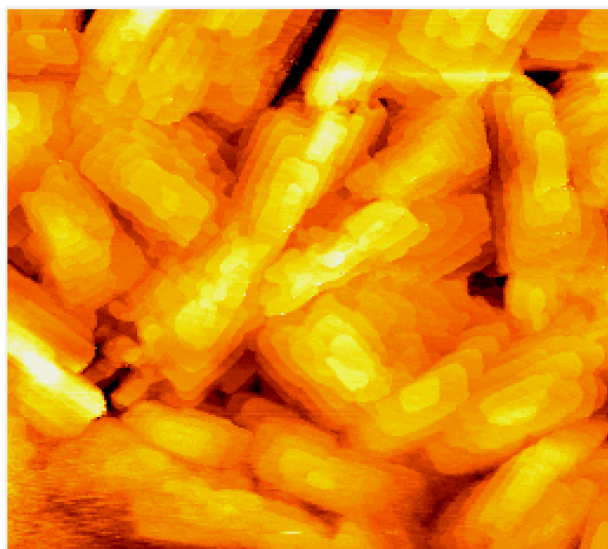
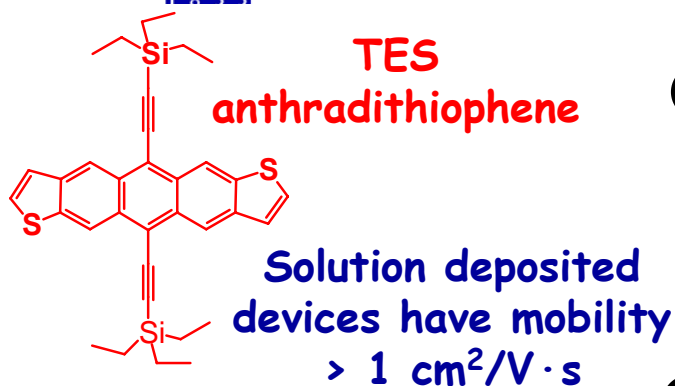
Solution-Processed Device Uniformity

Solution-processed device uniformity, reproducibility only fair, but improving

Device performance correlates well with film ordering

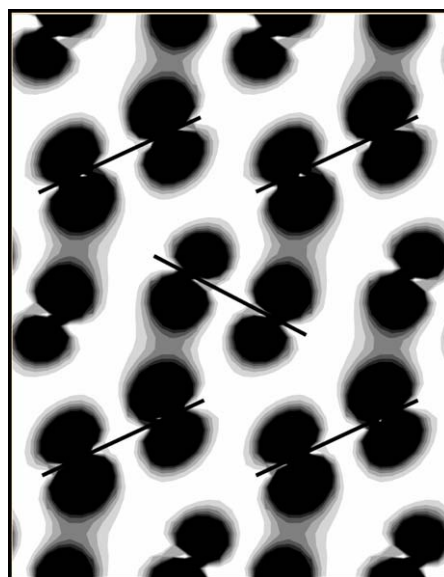
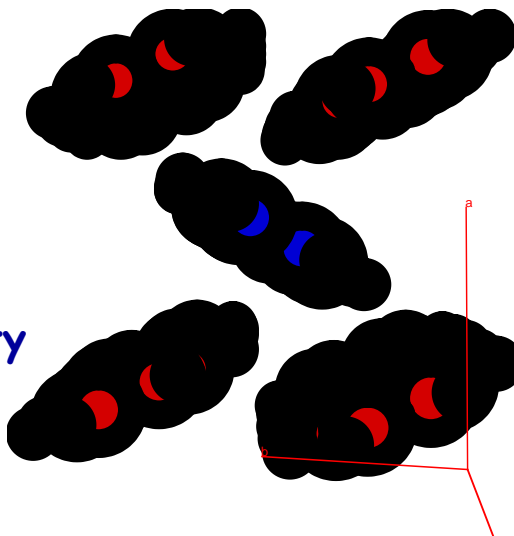
Film ordering sensitive to many factors - poorly understood





10 μm
80 nm evaporated TES ADT on OTS treated SiO_2

Well-ordered, but low mobility (10^{-3})



(K. Hummer, P. Puschnig, C. Ambrosch-Draxl, University of Austria, Gratz)

TFT current density

$$\text{TFT: } Q = E_{\text{gate}} \epsilon_{\text{ox}}$$

$$\text{SiO}_2 \epsilon_{\text{ox}} = 3.9\epsilon_0, E_{\text{max}} = 10^7 \text{ V/cm}$$

$$Q_{\text{max}} = 3.5 \times 10^{-6} \text{ C/cm}^2 \\ = 2.2 \times 10^{13} \text{ carriers/cm}^2$$

Sheet resistance of a sheet of charge $R_s = 1/(q\mu N_{\text{sheet}}) \Omega/\square$

Suppose $\mu = \sim 1 \text{ cm}^2/\text{V}\cdot\text{s}$

$$R_{s\text{min}} = 1/(q \times 2.2 \times 10^{13}) = \\ \sim 2.8 \times 10^5 \Omega/\square$$

Suppose $L = 1 \mu\text{m}$ & $V_{\text{DS}} = 10 \text{ V}$

Then $I_{\text{DS}} \sim 36 \mu\text{A}/\mu\text{m}$ or 0.36 A/cm

But channel is thin, $\leq 10 \text{ nm}$, so this is a current density of about $3.6 \times 10^5 \text{ A/cm}^2$

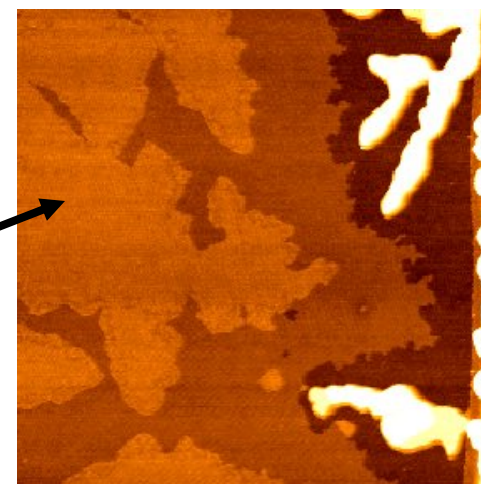
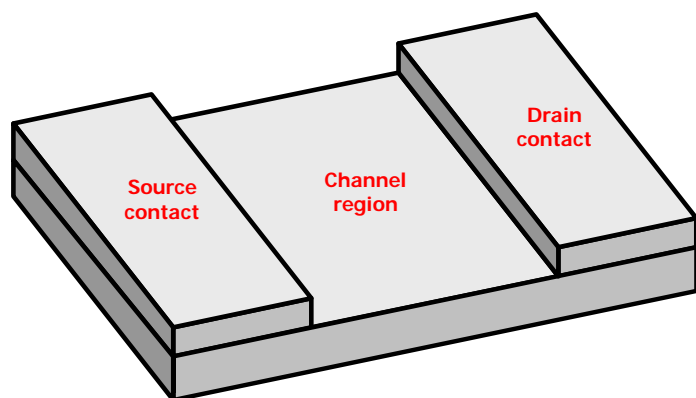
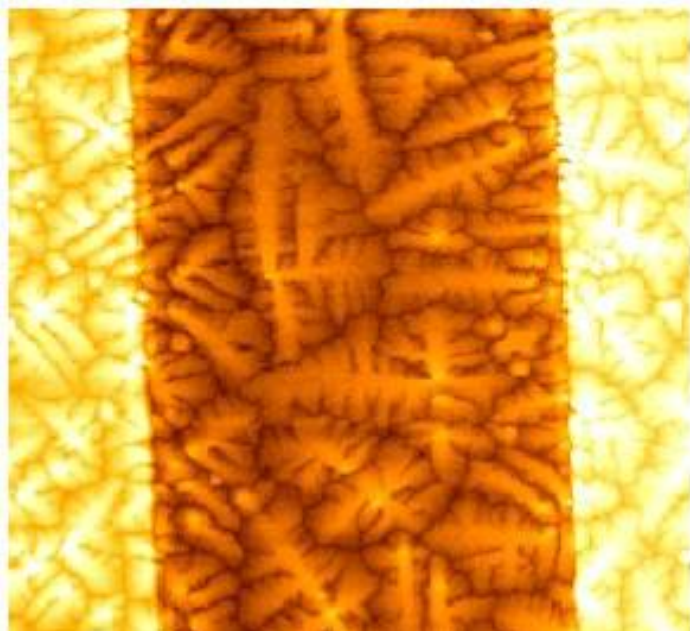
**Compare: OLEDs $\sim 1 \text{ A/cm}^2$
 organic laser $\sim 1000 \text{ A/cm}^2$**



Central Problem #1 - OTFT Contacts

Most organic semiconductors look a lot like insulators - contacts can be problematic

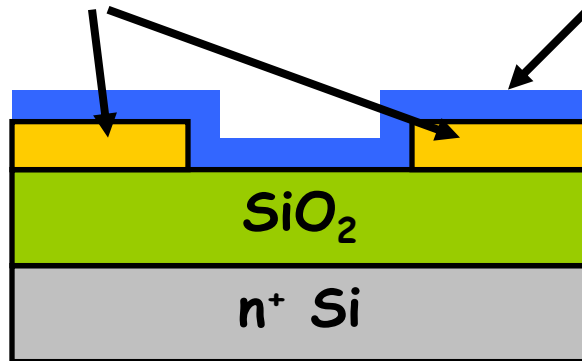
Details of film growth and morphology and device structure often amplify contact problems





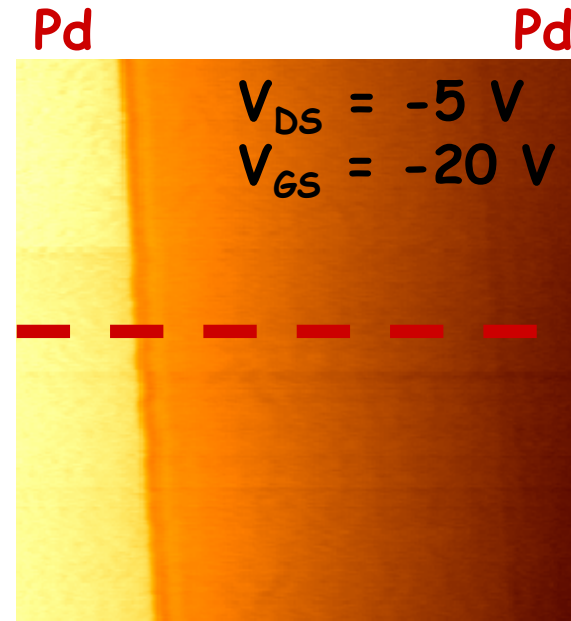
Pd Contacts

Pentacene

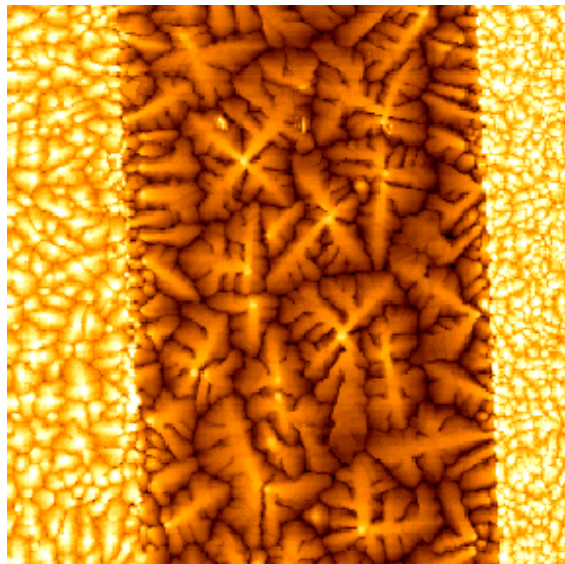


Bottom Contact TFT

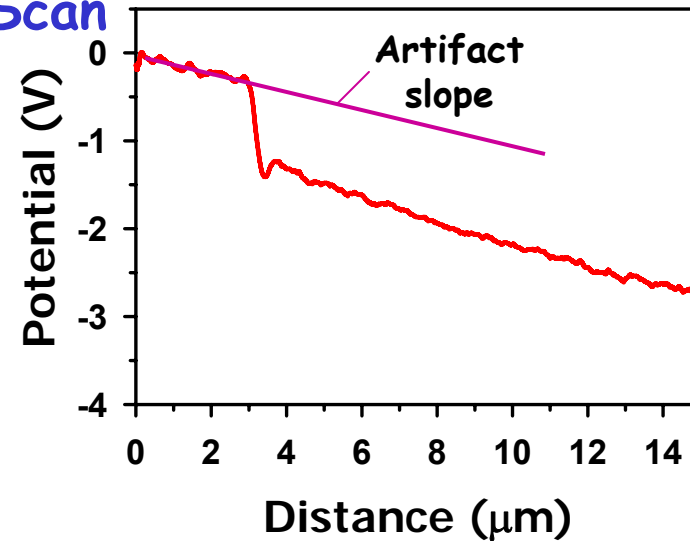
EFM



AFM

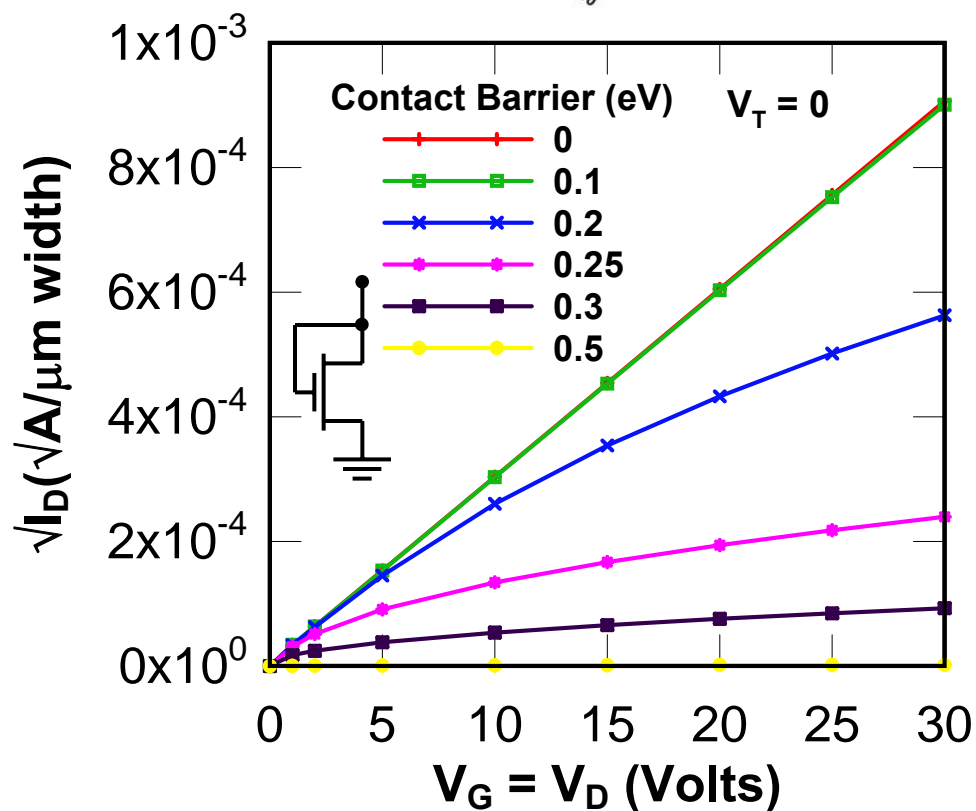
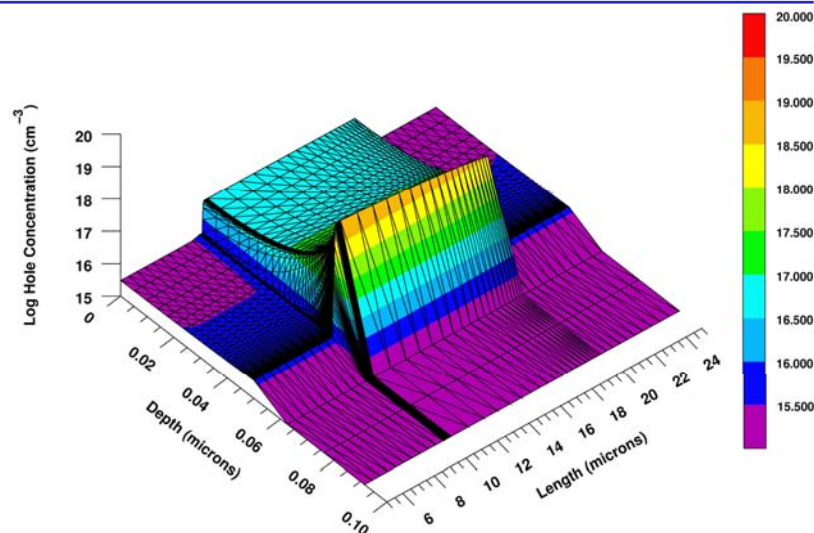
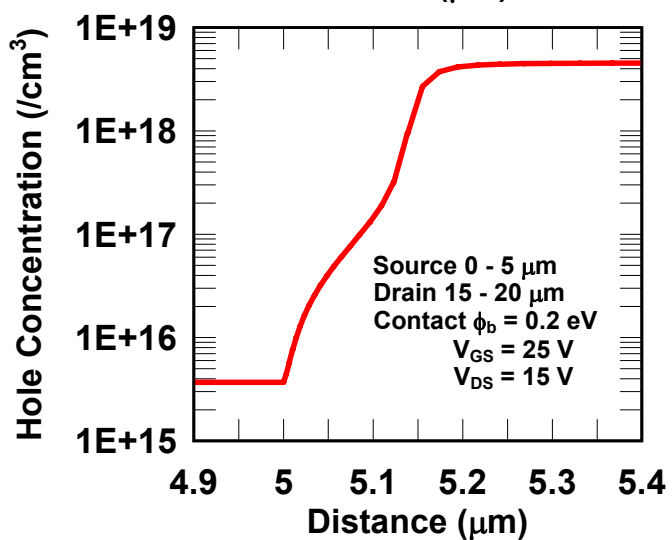
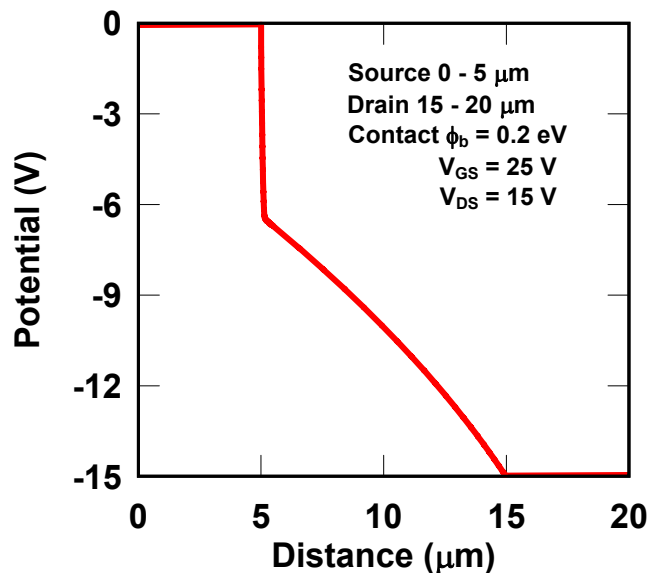
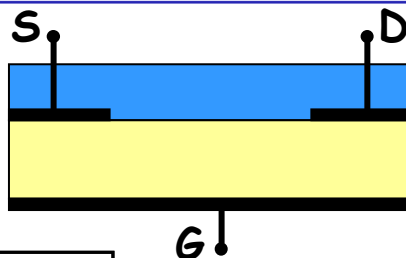


Line Scan



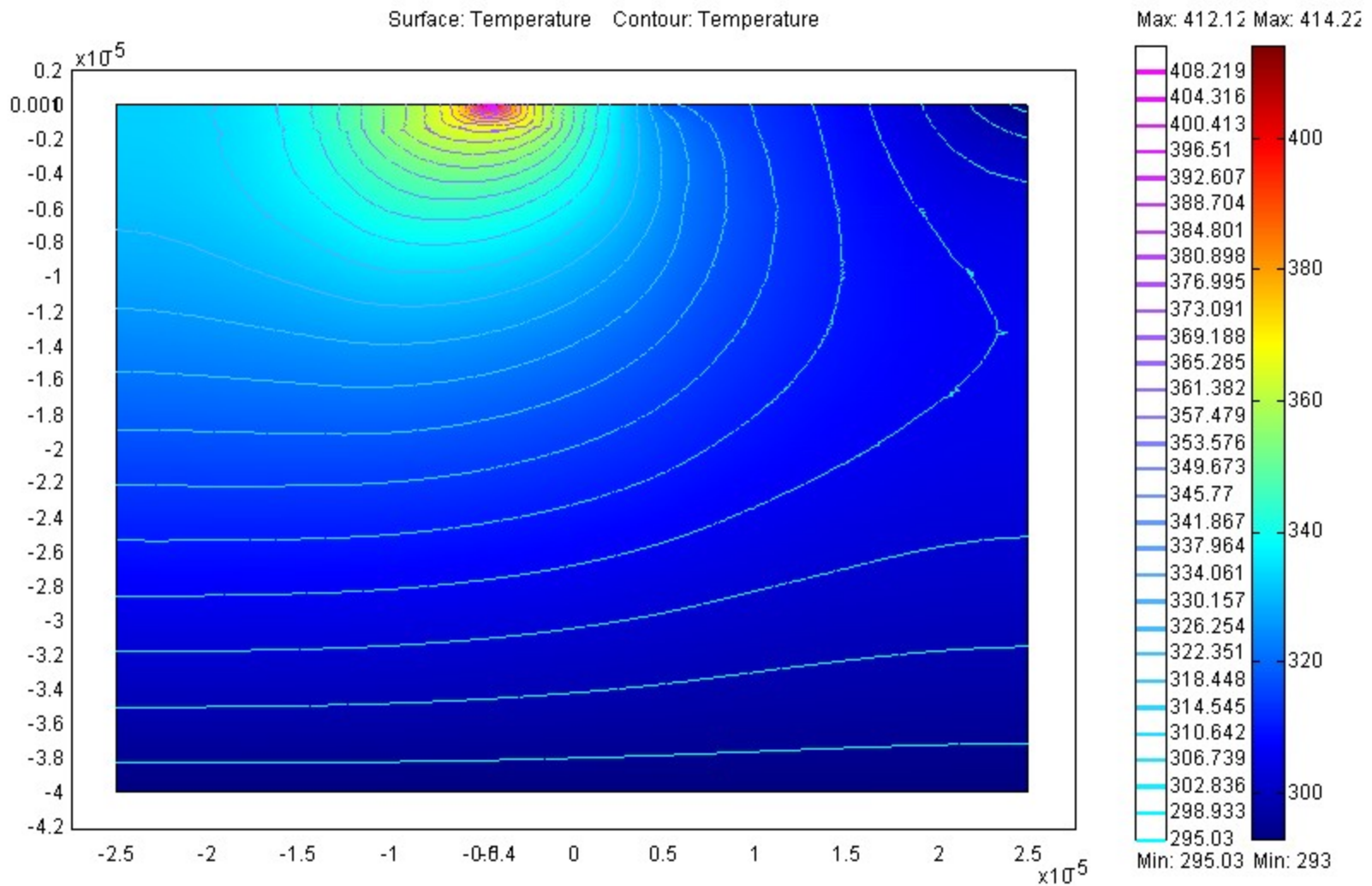


Contact Barriers





Contact Related Power Density





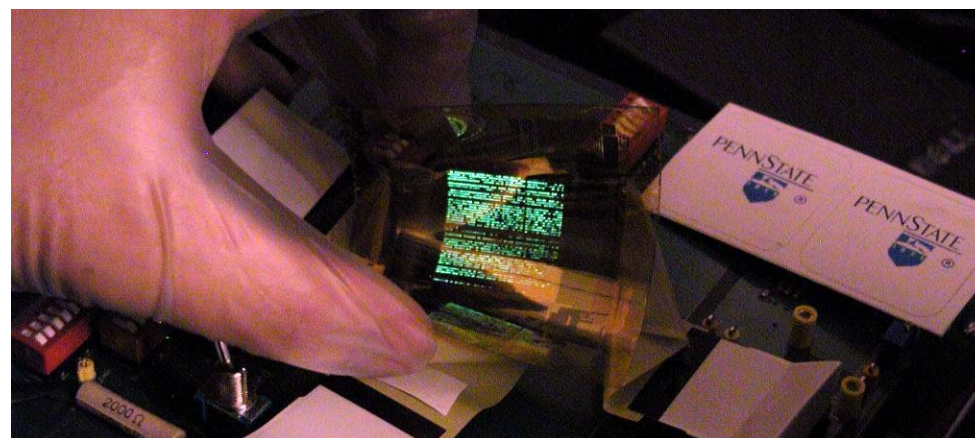
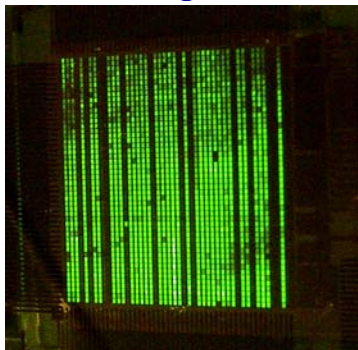
Central Problem #2 - Dielectrics





Lots of central problems?





- Polyimide substrate α -Si:H AMOLEDs
- ZnO conductors and semiconductors
- Polyester substrate organic circuits
- All organic displays
- High mobility solution-processed devices
- Improved materials likely
- Steps toward electronics anywhere!

• cost? cost? cost?

